

First-principles simulation of electrochemical reactions at solid-liquid interface

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07/03/2018

ISS2018@ISSP

Outline

- Introduction
- Simulation platform for electrochemical interface
 - Effective screening medium (**ESM**) method
 - Constant bias potential (**constant- μ_e**) method
 - Hybrid simulation method: DFT+liquid theory (**ESM-RISM**)
- Applications
 - Lithium Insertion/Desorption Reaction in Li-ion battery
- Summary
- Appendix (How to define the electrode potential from DFT)

Electrochemical devices/engineering



Battery

- Manganese dry cell
- Lead battery
- NiCd, NiH secondary battery
- Fuel cell
- Lithium secondary battery

Capacitor

- Electrolytic condenser
- Double layer condenser
- Supercapacitor

Photovoltaic cell

- c-Si, a-Si solar cell
- Dye sensitized solar cell

photoelectrochemical
hydrogen production

Sensor

- pH meter
- ion selective concentration meter
- glucose, etc. (using enzyme)
- gas (oxygen, etc.)



Electroplating

Cathodic protection

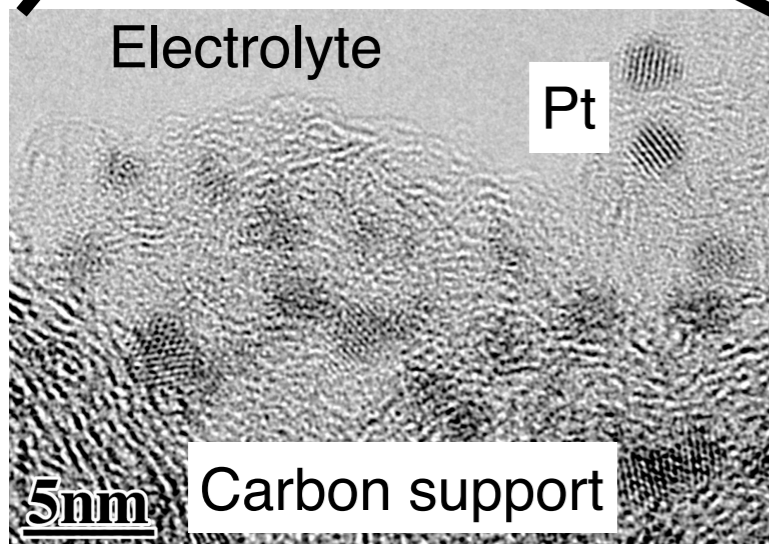
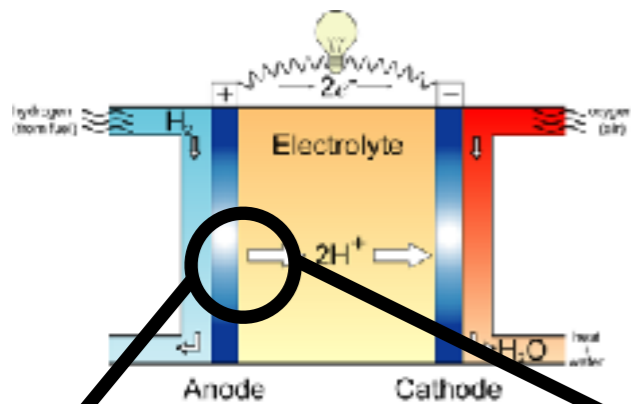


Electrolysis

- Aluminum, Copper, etc.
- Water, salt, etc.
- Organic chemicals
- tetraethyl lead

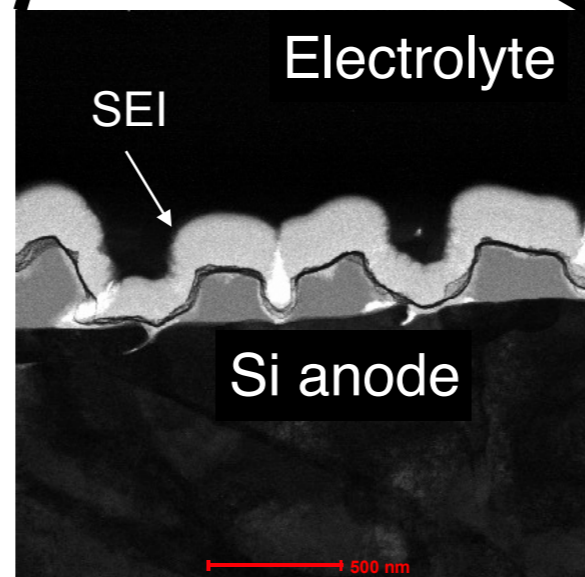
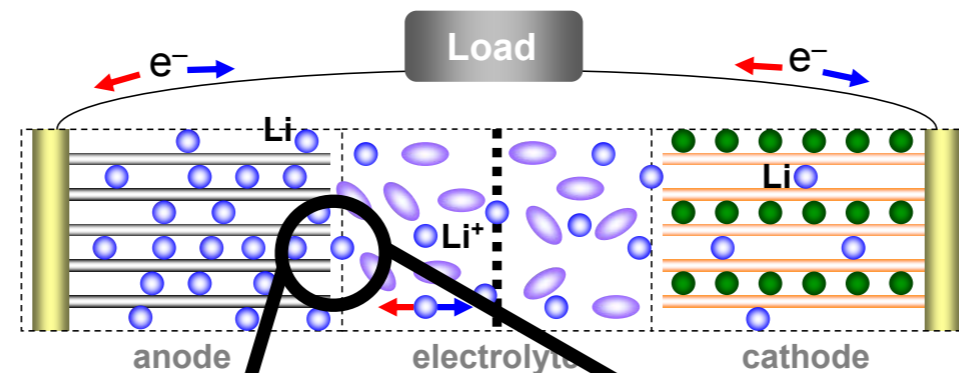
Target systems

Energy generation (Fuel cell)



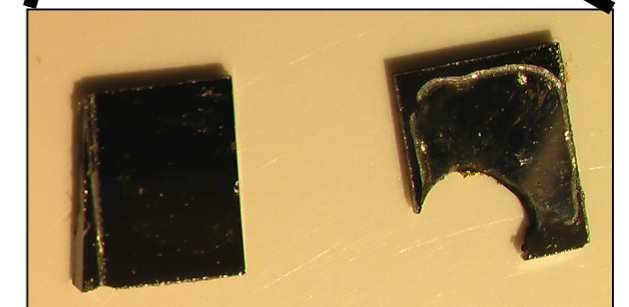
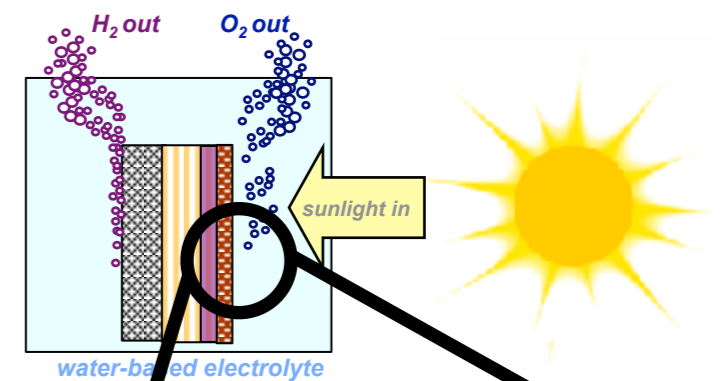
- overpotential
- a cheaper alternative to Pt

Energy storage (Secondary battery)



- formation mechanism of SEI
- interface resistance

Energy harvesting (PV, PEC)



24 hour

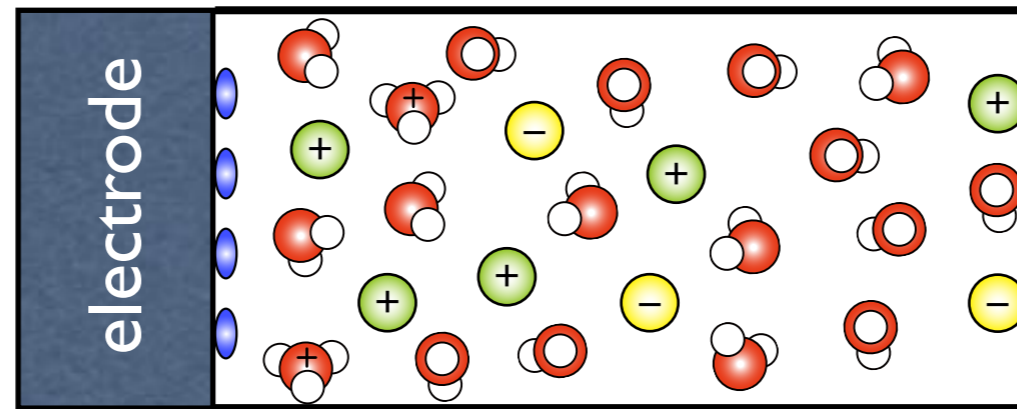
- corrosion mechanism
- surface modification

Electrochemical interface

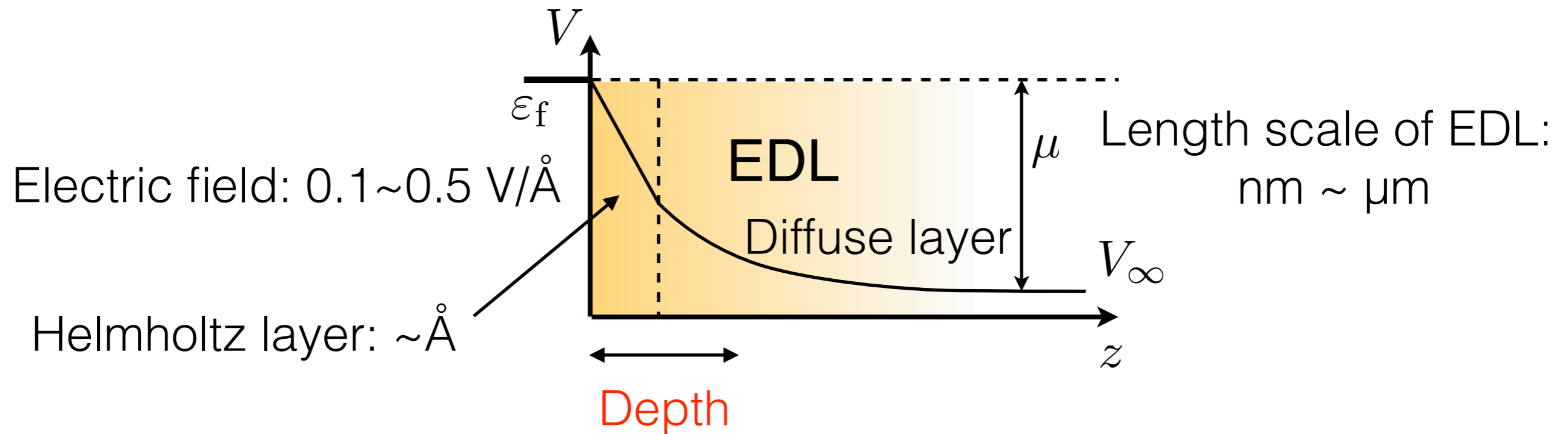
25°C, 1.0M NaCl, Electrode: Pt

4 nm² surface area

3-layer Pt(111):
460Pt atoms

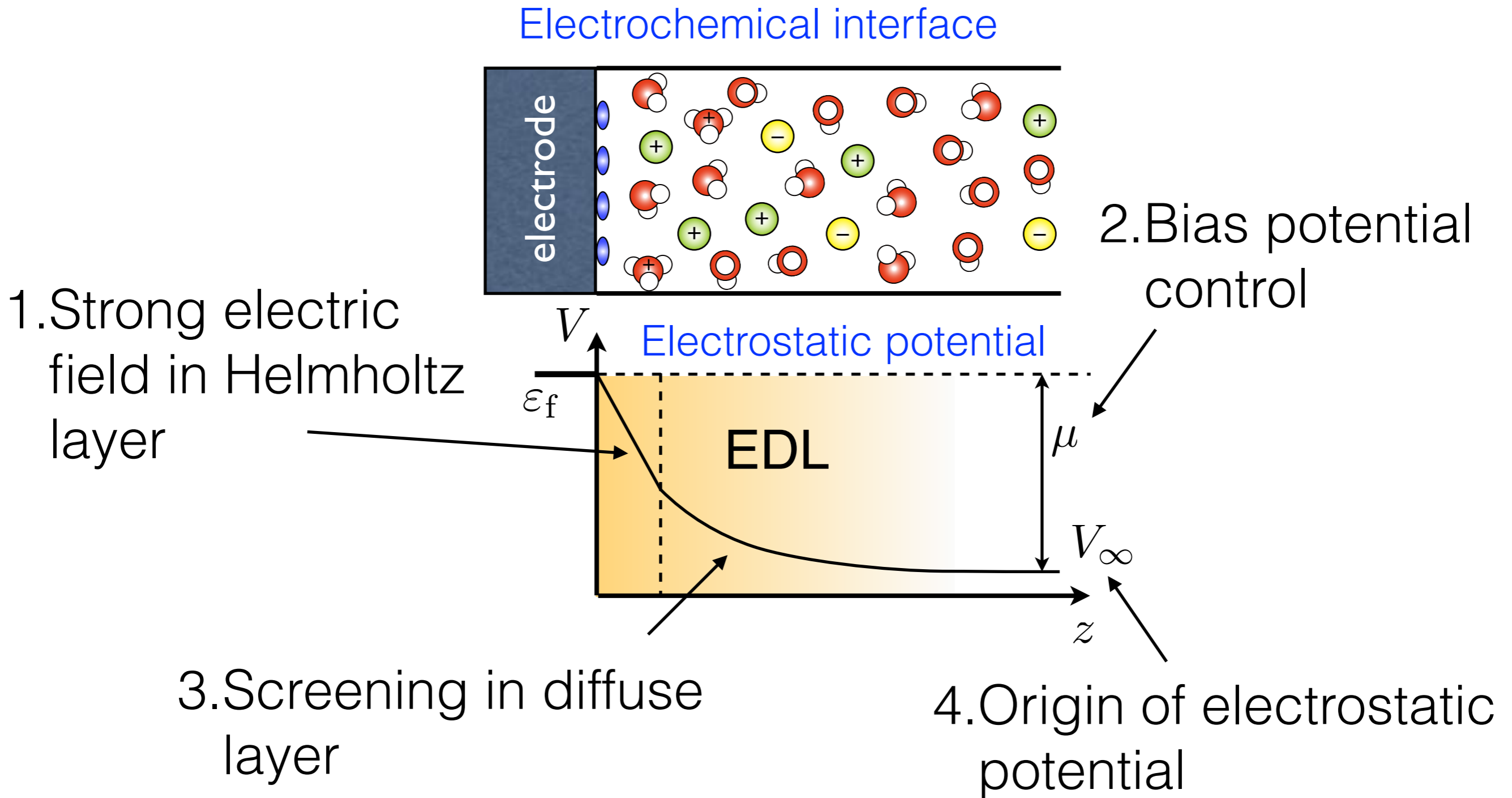


1 NaCl / 50 H₂O



2 nm: 800 atoms (264 H₂O, 5 NaCl)
 10 nm: 5000 atoms (1320 H₂O, 25 NaCl)
 0.1 μm: 50000 atoms (13200 H₂O, 250 NaCl)

4 Challenges in modeling an electrochemical reaction for DFT-MD



4 Challenges in modeling an electrochemical reaction for DFT-MD

1. Strong electric field in Helmholtz layer

ESM method

Effective Screening Medium method
Phys. Rev. B **73**, 115407 (2006)

2. Bias potential control

Constant- μ_e method

Phys. Rev. Lett. **109**, 266101 (2012)

3. Screening in diffuse layer

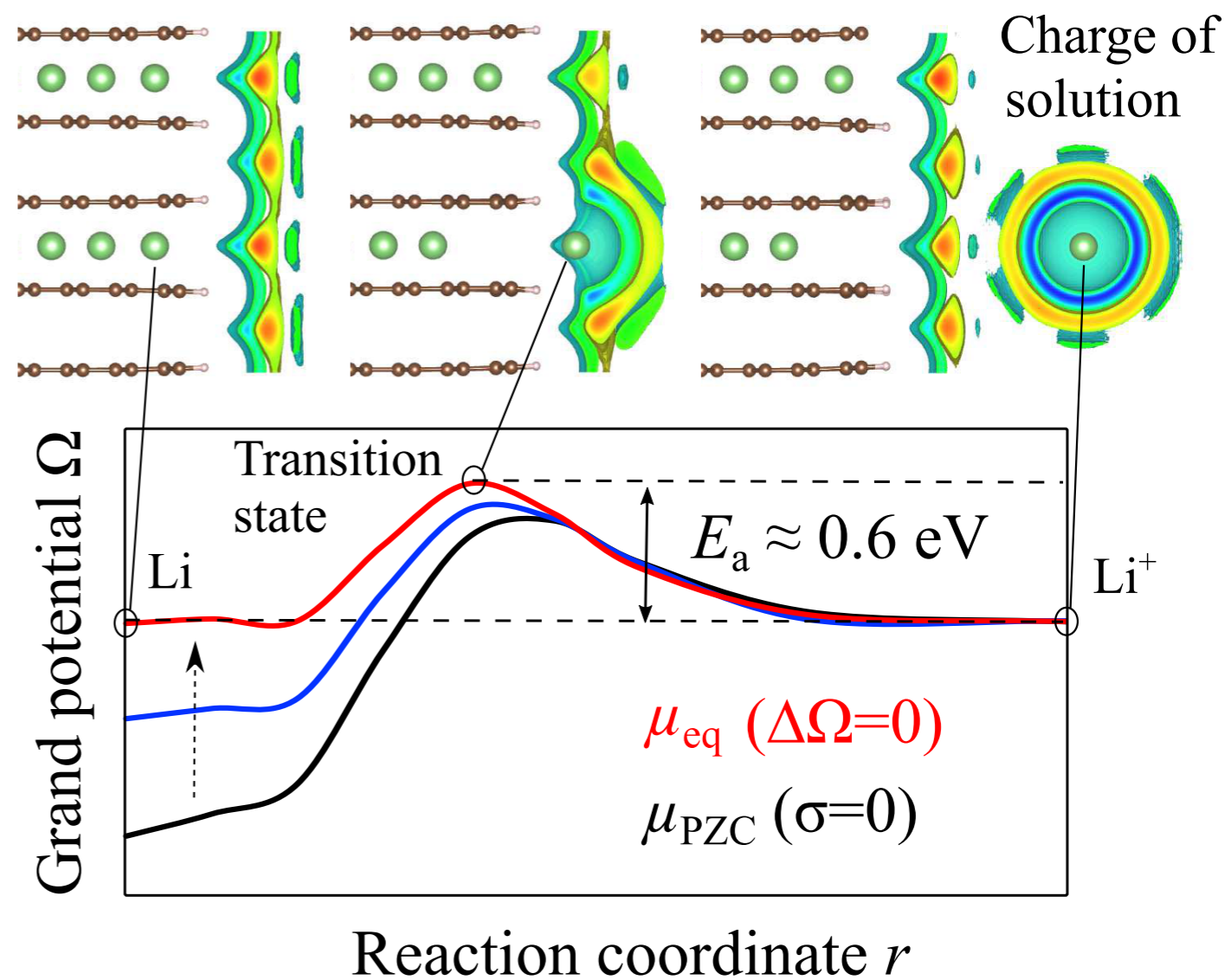
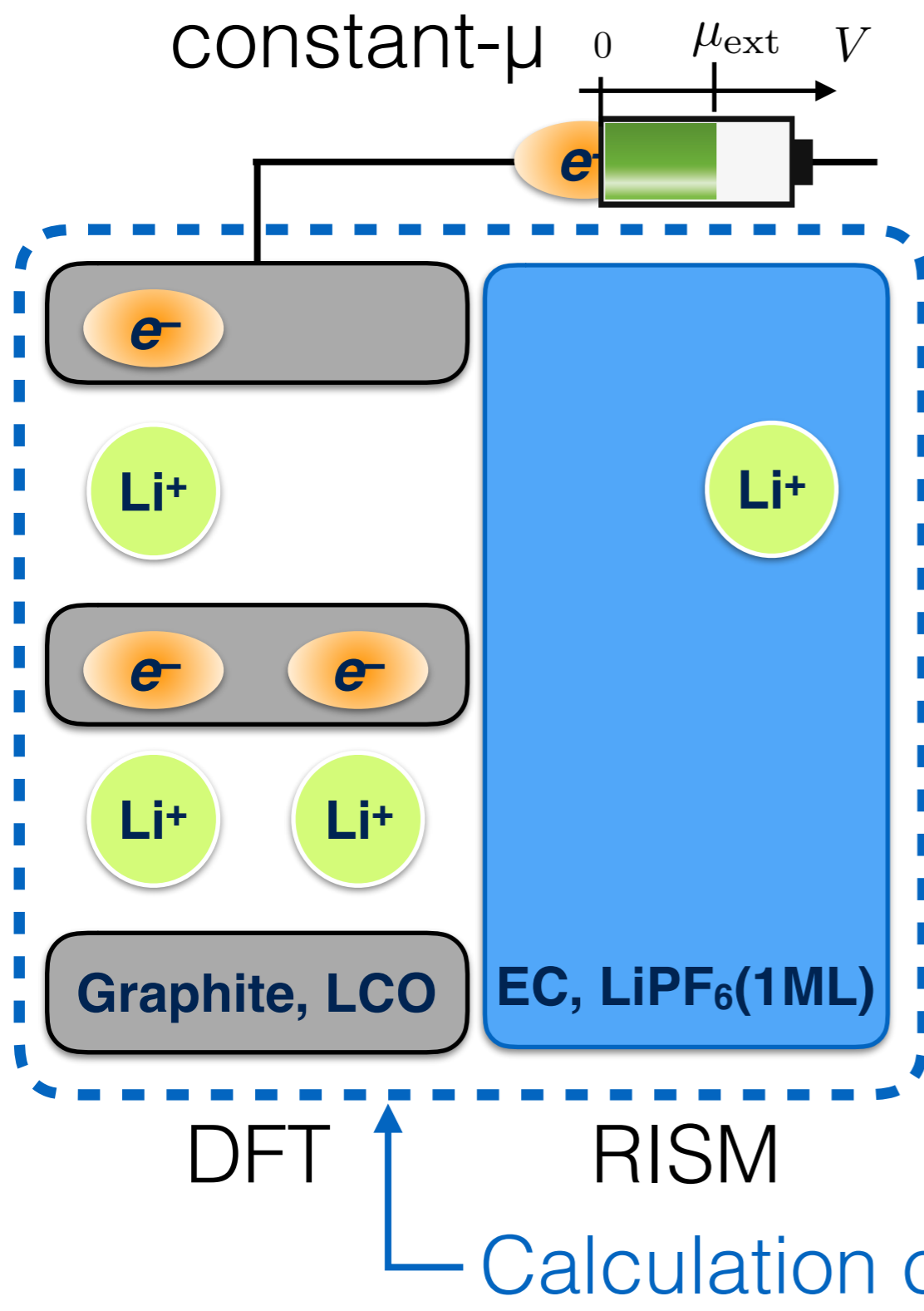
ESM-RISM method

Reference Interaction Site Model

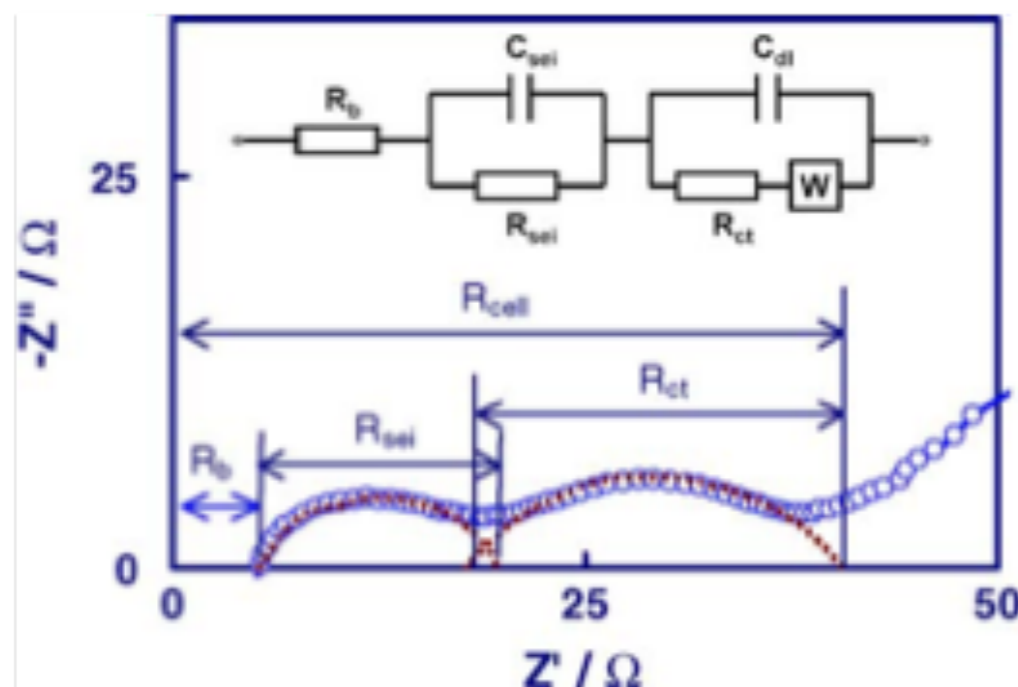
4. Origin of electrostatic potential

Phys. Rev. B **96**, 115429 (2017)

Solvation process of Li-ion



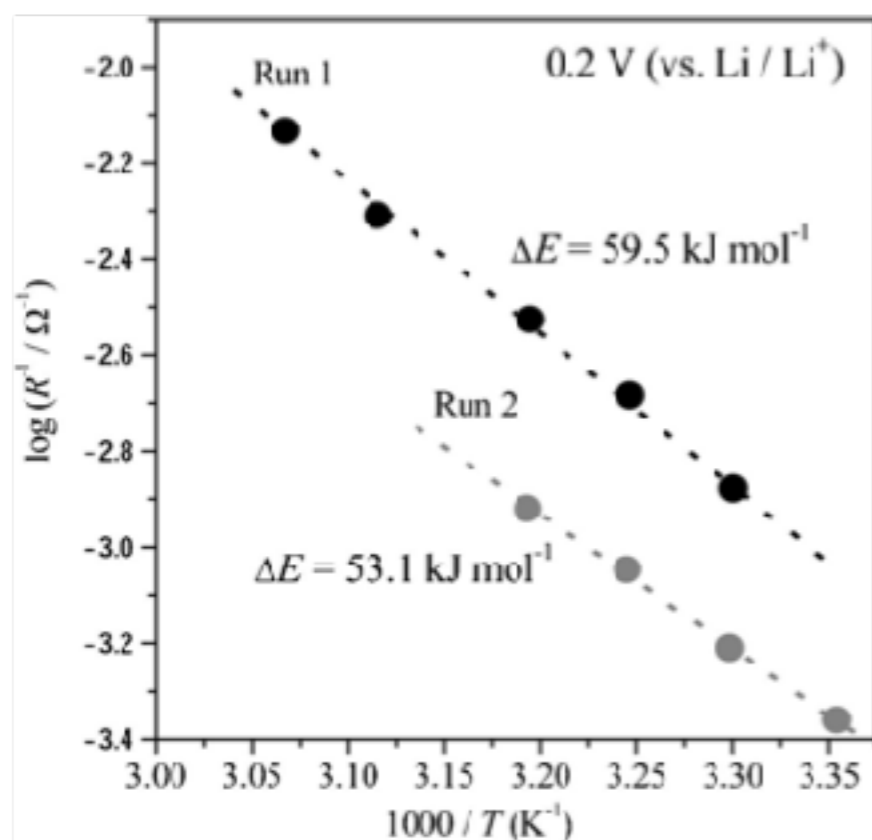
Electrochemical impedance spectroscopy (EIS) measurements



Typical EIS of Conventional LIB cell
LiCoO₂ | EC3:EMC7 LiPF₆ 1M | Graphite

In the fully charged and discharged states as well as at the low temperatures ($\leq 20^\circ\text{C}$), the R_{cell} of the Li-ion cells is **predominated** by the R_{ct} .

S. S. Zhang, K. Xu, and T. R. Jow, *Electrochimica Acta* **49**, 1057 (2004).



Temperature-dependence of R_{ct} @ $0.2 \text{ V vs. Li/Li}^+$

The activation energies were evaluated to be around 50-60 kJ/mol (**0.5-0.6 eV**). These values are very large compared to lithium ion conduction in active materials.

T. Abe, H. Fukuda, Y. Iriyama, and Z. Ogumi, *J. Electrochem. Soc.* **151**, A1120 (2004).

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Total energy functional in conventional method

Total energy functional

$$E[\rho_e] = T[\rho_e] + E_{xc}[\rho_e] + \frac{1}{2} \iint d\mathbf{r}d\mathbf{r}' \frac{\rho_e(\mathbf{r})\rho_e(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} + \int d\mathbf{r} v_{\text{ext}}(\mathbf{r})\rho_e(\mathbf{r}) + E_{\text{II}}$$

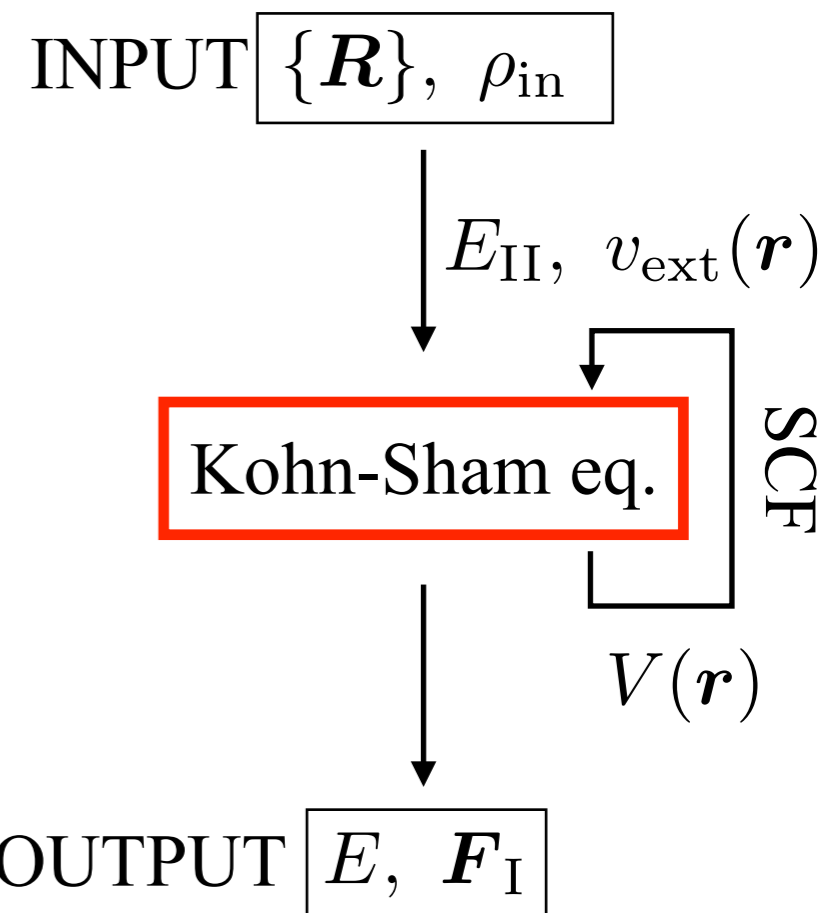
$\frac{\delta E}{\delta \rho_e} = 0$ ↓ Kohn-Sham equation

$$\left[-\frac{1}{2} \nabla^2 + V(\mathbf{r}) + \hat{V}_{\text{NL}} + V_{\text{xc}}(\mathbf{r}) \right] \psi_i(\mathbf{r}) = \varepsilon_i \psi_i(\mathbf{r})$$

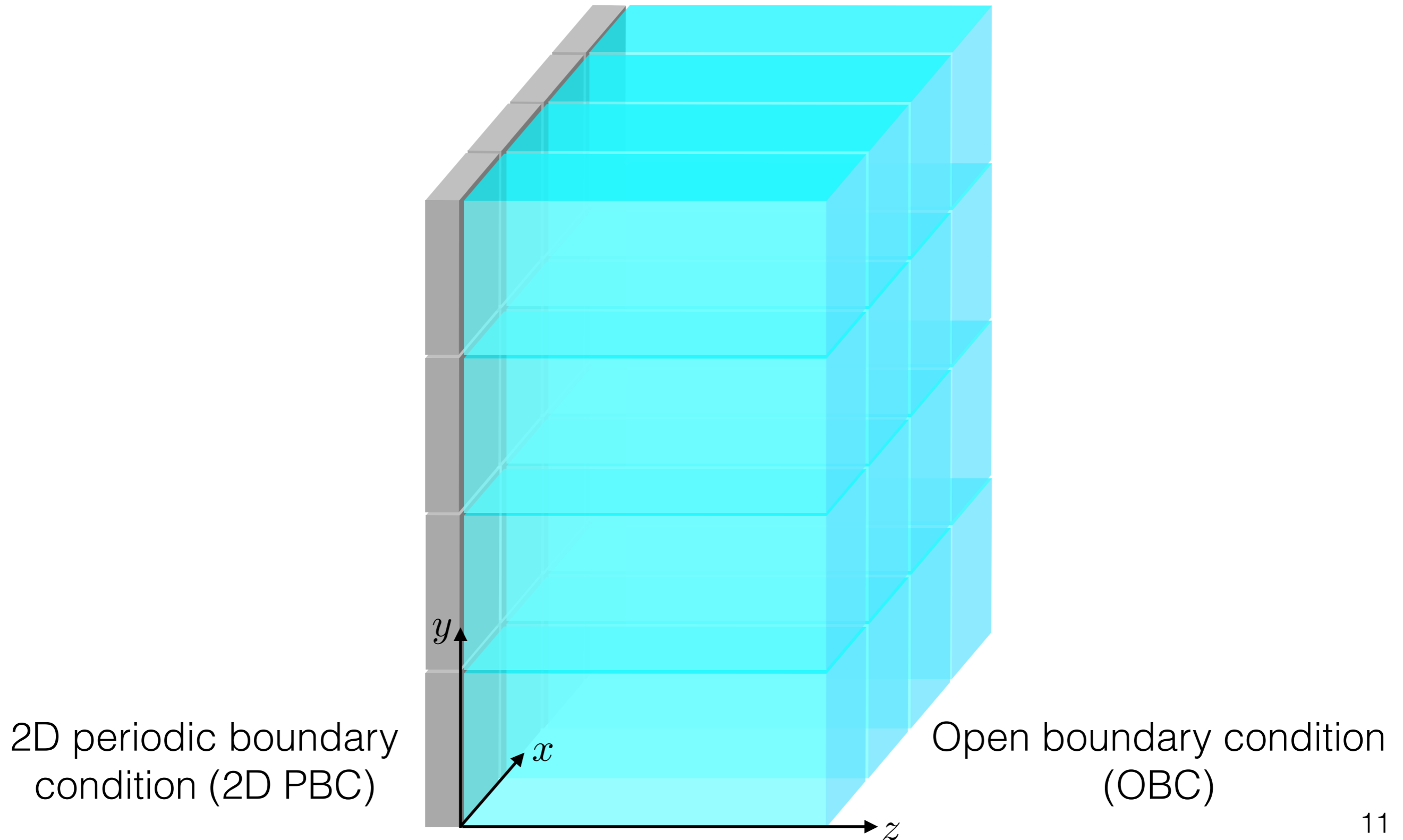
Poisson equation is solved with **periodic boundary condition** in advance and use the following expression

$$V(\mathbf{r}) = \int d\mathbf{r}' \frac{\rho_{\text{tot}}(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} = \int d\mathbf{r}' G^{\text{PBC}}(\mathbf{r}, \mathbf{r}') \rho_{\text{tot}}(\mathbf{r}')$$

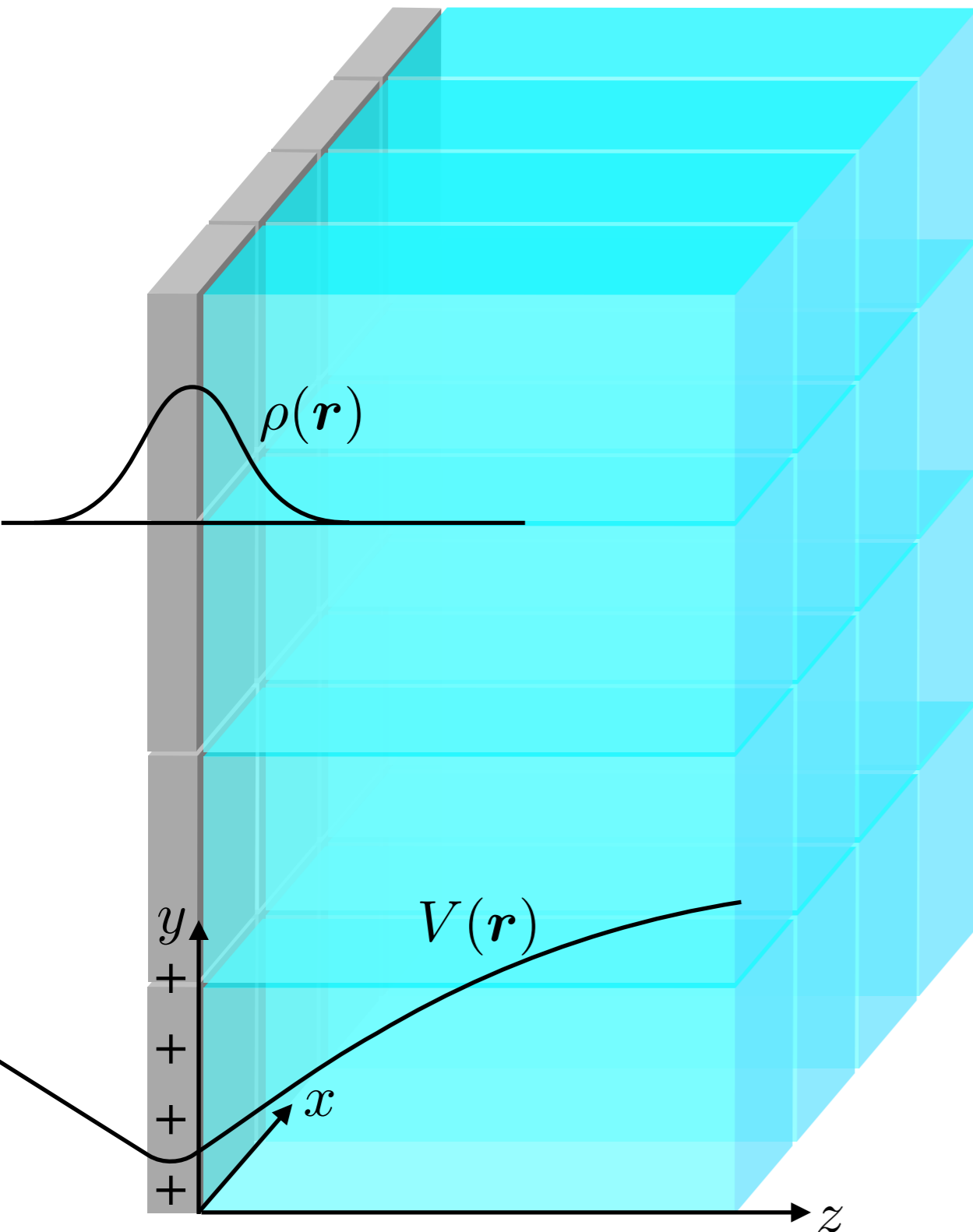
Need to solve Poisson eq. with **different BC.**



Boundary condition at the interface



Boundary condition at the interface



- In the density functional theory (DFT), we need to solve two equations.

Kohn-Sham equation

$$\left[-\frac{1}{2}\nabla^2 + V(\mathbf{r}) + \hat{V}_{\text{NL}} + V_{\text{xc}}(\mathbf{r}) \right] \psi_i(\mathbf{r}) = \varepsilon_i \psi_i(\mathbf{r})$$

→ 3D PBC

Poisson equation

$$\nabla[\epsilon(\mathbf{r})\nabla]V(\mathbf{r}) = -4\pi\rho_{\text{tot}}(\mathbf{r})$$

→ 2D PBC + OBC



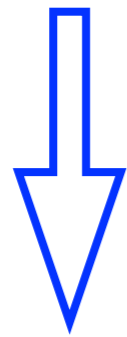
Mixed boundary condition (MBC)

Effective screening medium (ESM)

M.O. and O. Sugino, PRB 73, 115407 (2006)

How to solve the poisson equation under MBC?

$$\nabla[\epsilon(\mathbf{r})\nabla]V(\mathbf{r}) = -4\pi\rho_{\text{tot}}(\mathbf{r})$$



Laue representation

$$[\partial_z\{\epsilon(z)\partial\} - \epsilon(z)g_{||}^2]V(\mathbf{g}_{||}, z) = -4\pi\rho(\mathbf{g}_{||}, z)$$

$$[\partial_z\{\epsilon(z)\partial\} - \epsilon(z)g_{||}^2]G(\mathbf{g}_{||}, z, z') = -4\pi\delta(\mathbf{g}_{||}, z - z')$$

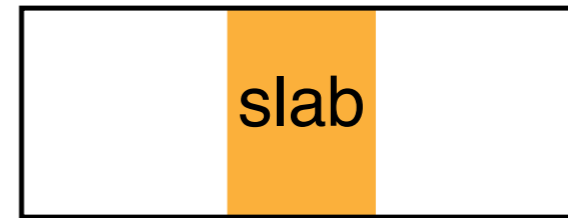
We can get Green's function analytically with each boundary conditions.

Effective screening medium (ESM)

M.O. and O. Sugino, PRB 73, 115407 (2006)

(i)

$$\partial_z V(g_{\parallel}, z)|_{z=\pm\infty} = 0, \quad \epsilon(z) = 1$$

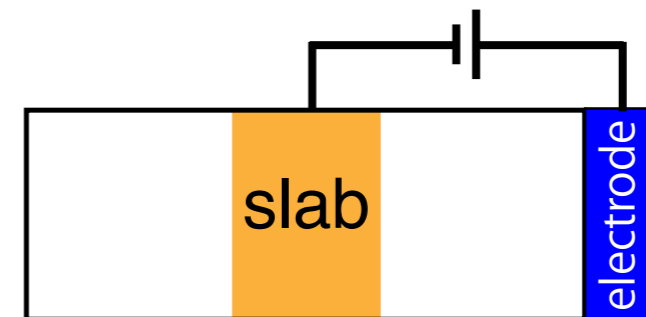


neutral surface, polarized surface...

(ii)

$$\begin{cases} V(g_{\parallel}, z_1) = 0 \\ \partial_z V(g_{\parallel}, z)|_{z=-\infty} = 0 \end{cases}$$

$$\epsilon(z) = \begin{cases} 1 & \text{if } z \geq z_1 \\ \infty & \text{if } z \leq z_1 \end{cases}$$

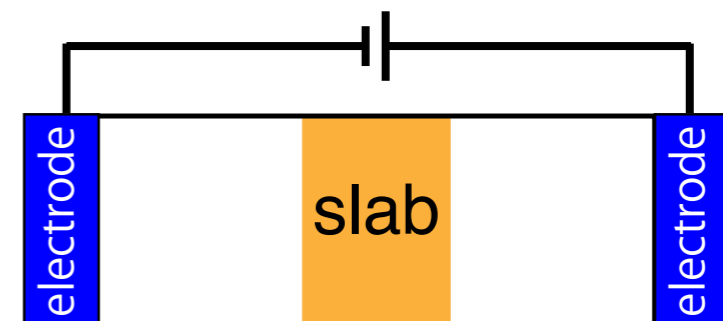


STM, gate electrode...

(iii)

$$\begin{cases} V(g_{\parallel}, z_1) = 0 \\ V(g_{\parallel}, -z_1) = V_0 \end{cases}$$

$$\epsilon(z) = \infty \quad \text{if } |z| \geq z_1$$



nano-structure in capacitor, zigzag pot.

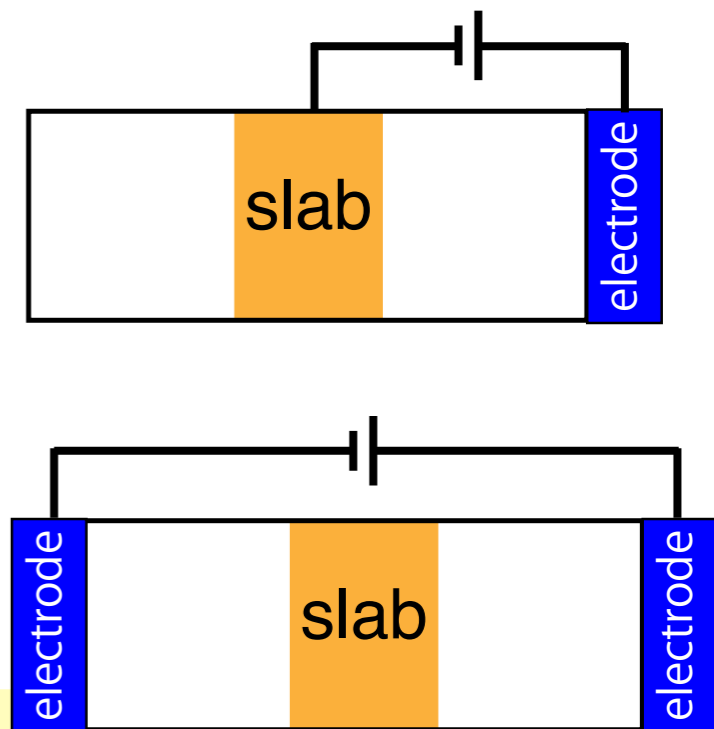
Effective screening medium (ESM)

M.O. and O. Sugino, PRB 73, 115407 (2006)

$$G^{(i)}(g_{\parallel}, z, z') = \frac{4\pi}{2g_{\parallel}} e^{-g_{\parallel}|z-z'|}$$

$$G^{(ii)}(g_{\parallel}, z, z') = \frac{4\pi}{2g_{\parallel}} e^{-g_{\parallel}|z-z'|} - \frac{4\pi}{2g_{\parallel}} e^{-g_{\parallel}(2z_1-z-z')}$$

$$G^{(iii)}(g_{\parallel}, z, z') = \frac{4\pi}{2g_{\parallel}} e^{-g_{\parallel}|z-z'|} + \frac{4\pi}{2g_{\parallel}} \frac{e^{-2g_{\parallel}z_1} \cosh\{g_{\parallel}(z-z')\} - \cosh\{g_{\parallel}(z+z')\}}{\sinh(2g_{\parallel}z_1)}$$



Total energy functional of the ESM method

Total energy functional

$$E[\rho] = T[\rho] + E_{\text{xc}}[\rho] + \frac{1}{2} \iint d\mathbf{r} d\mathbf{r}' \frac{\rho(\mathbf{r})\rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} + \int d\mathbf{r} v_{\text{ext}}(\mathbf{r})\rho(\mathbf{r}) + E_{\text{ion}}$$

$V \rightsquigarrow$ variable

$$E[\rho_e, V] = T[\rho_e] + E_{\text{xc}}[\rho_e] + \int d\mathbf{r} \left[+\frac{\epsilon(\mathbf{r})}{8\pi} |\nabla V(\mathbf{r})|^2 + \rho_{\text{tot}}(\mathbf{r})V(\mathbf{r}) \right]$$

$$\frac{\delta E}{\delta V} = 0$$

Generalized Poisson equation

$$\nabla[\epsilon(\mathbf{r})\nabla]V(\mathbf{r}) = -4\pi\rho_{\text{tot}}(\mathbf{r})$$

conventional

$$\epsilon(\mathbf{r}) = 1$$

$$V(\mathbf{r}) = \int d\mathbf{r}' \frac{\rho_{\text{tot}}(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|}$$

$$\frac{\delta E}{\delta \rho_e} = 0$$

Kohn-Sham equation

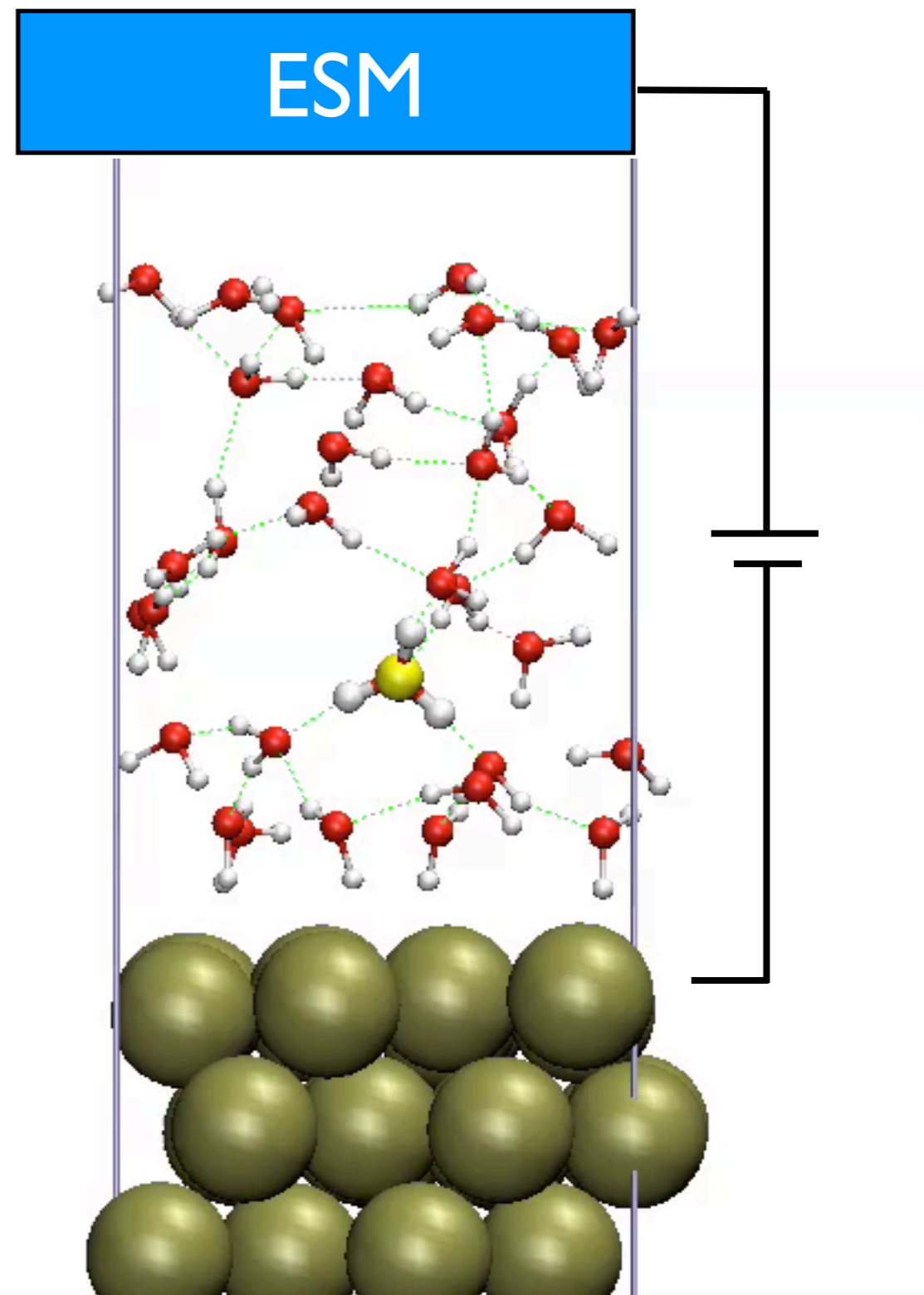
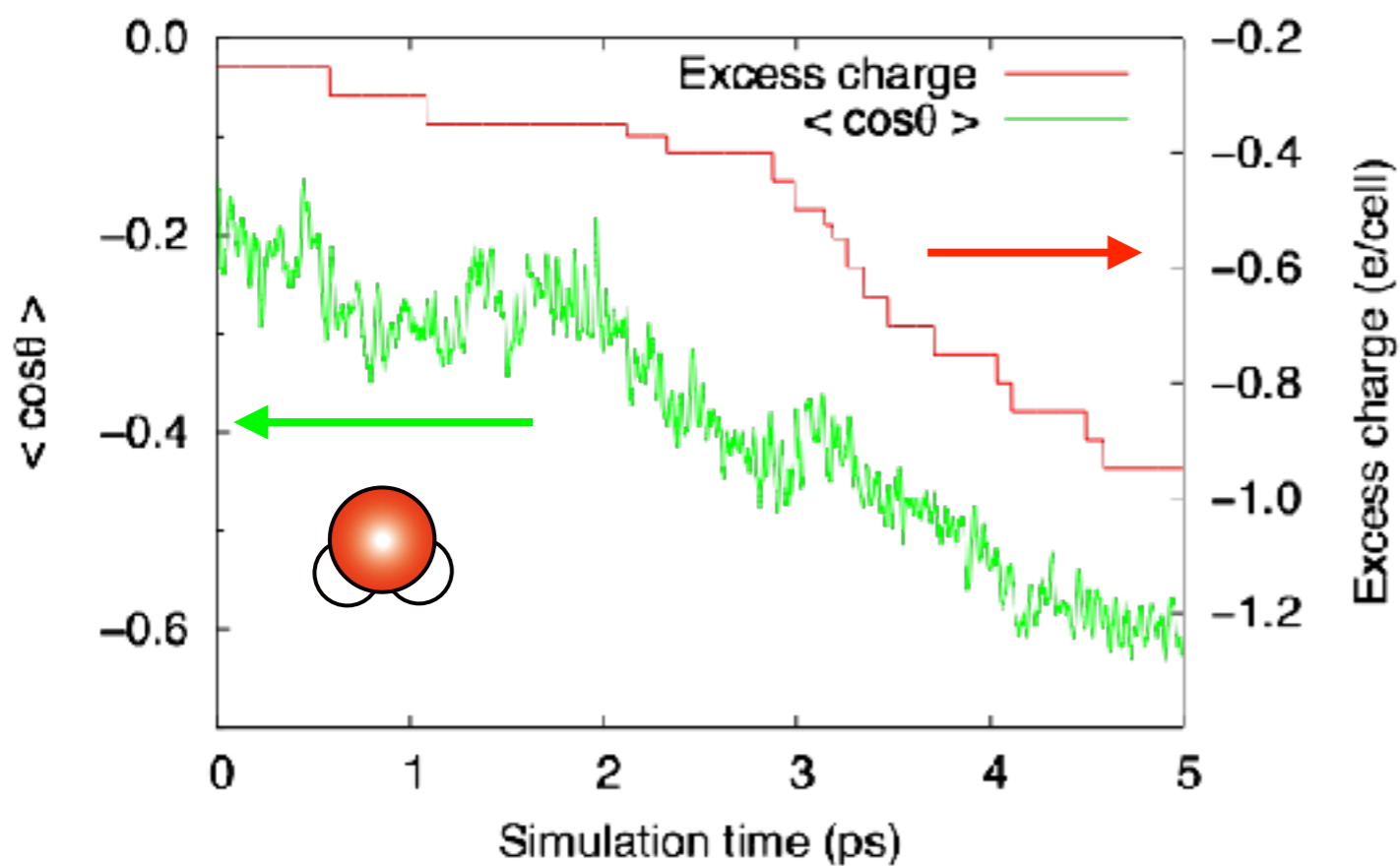
$$\left[-\frac{1}{2}\nabla^2 + V(\mathbf{r}) + \hat{V}_{\text{NL}} + V_{\text{xc}}(\mathbf{r}) \right] \psi_i(\mathbf{r}) = \epsilon_i \psi_i(\mathbf{r})$$

ESM

$$\epsilon(\mathbf{r}) : \text{model dependent}$$

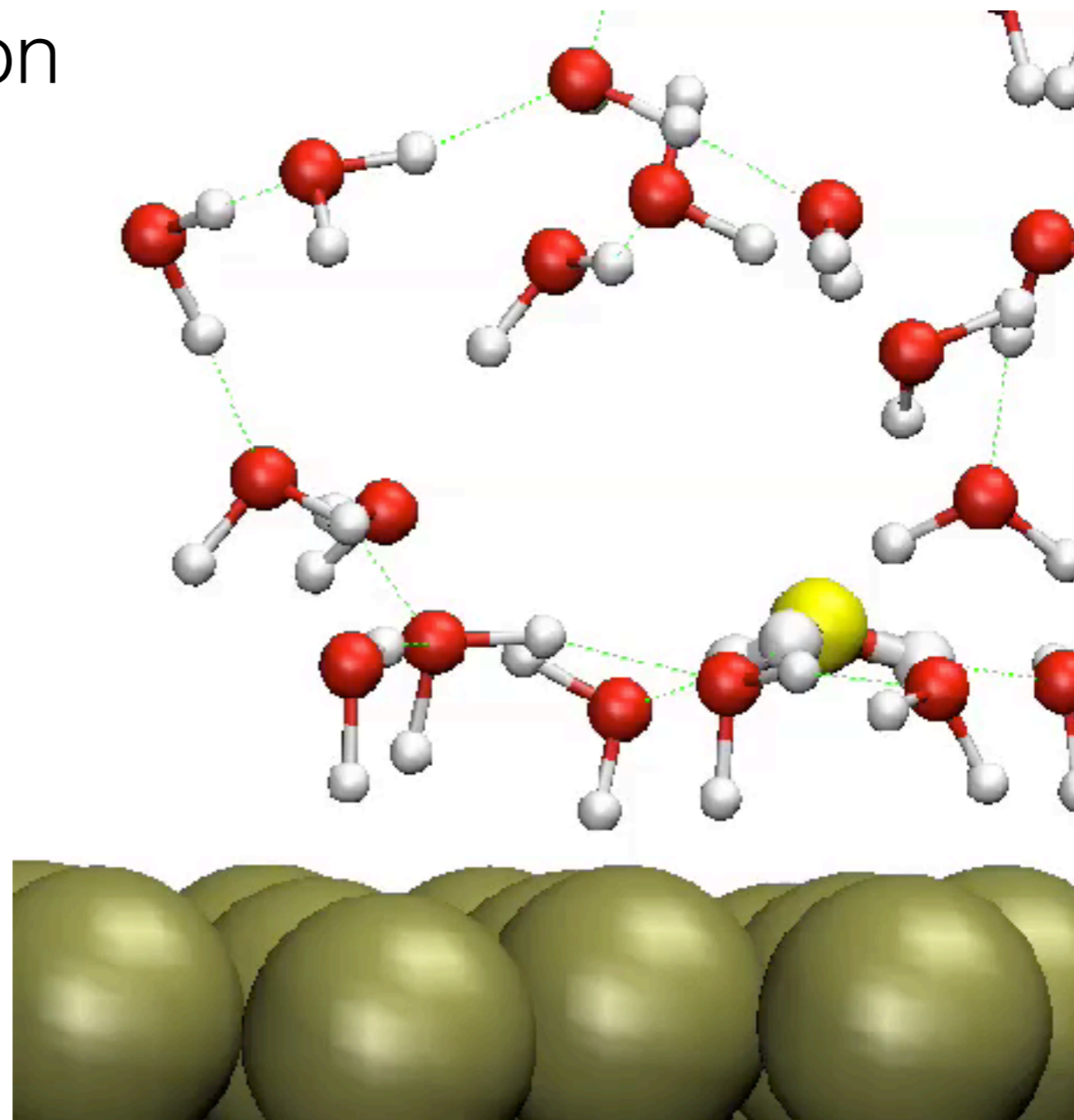
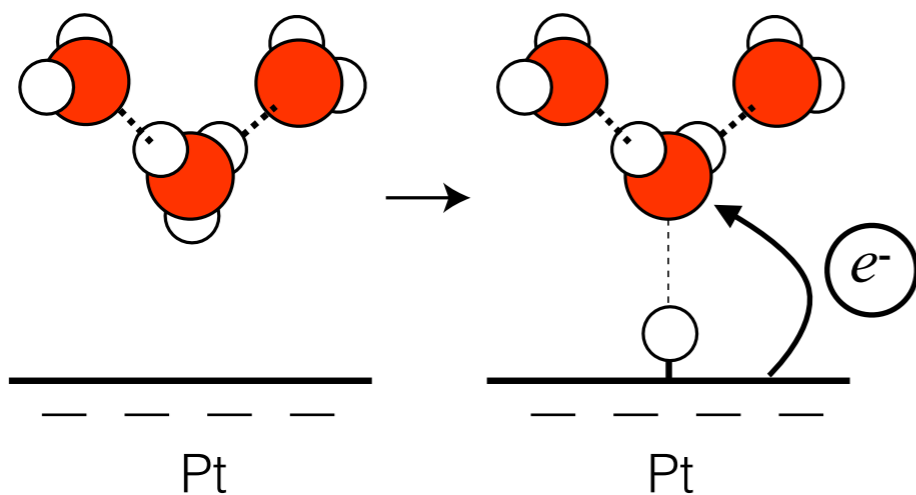
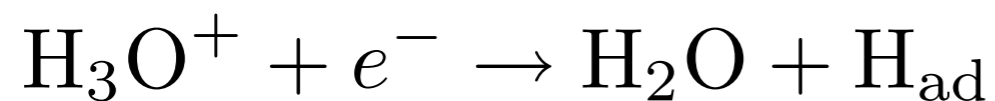
$$V(\mathbf{r}) = \int d\mathbf{r}' G(\mathbf{r}, \mathbf{r}')\rho_{\text{tot}}(\mathbf{r}')$$

Schematic animation of electrochemical interface simulation



Electrochemical reaction

Hydrogen adsorption reaction

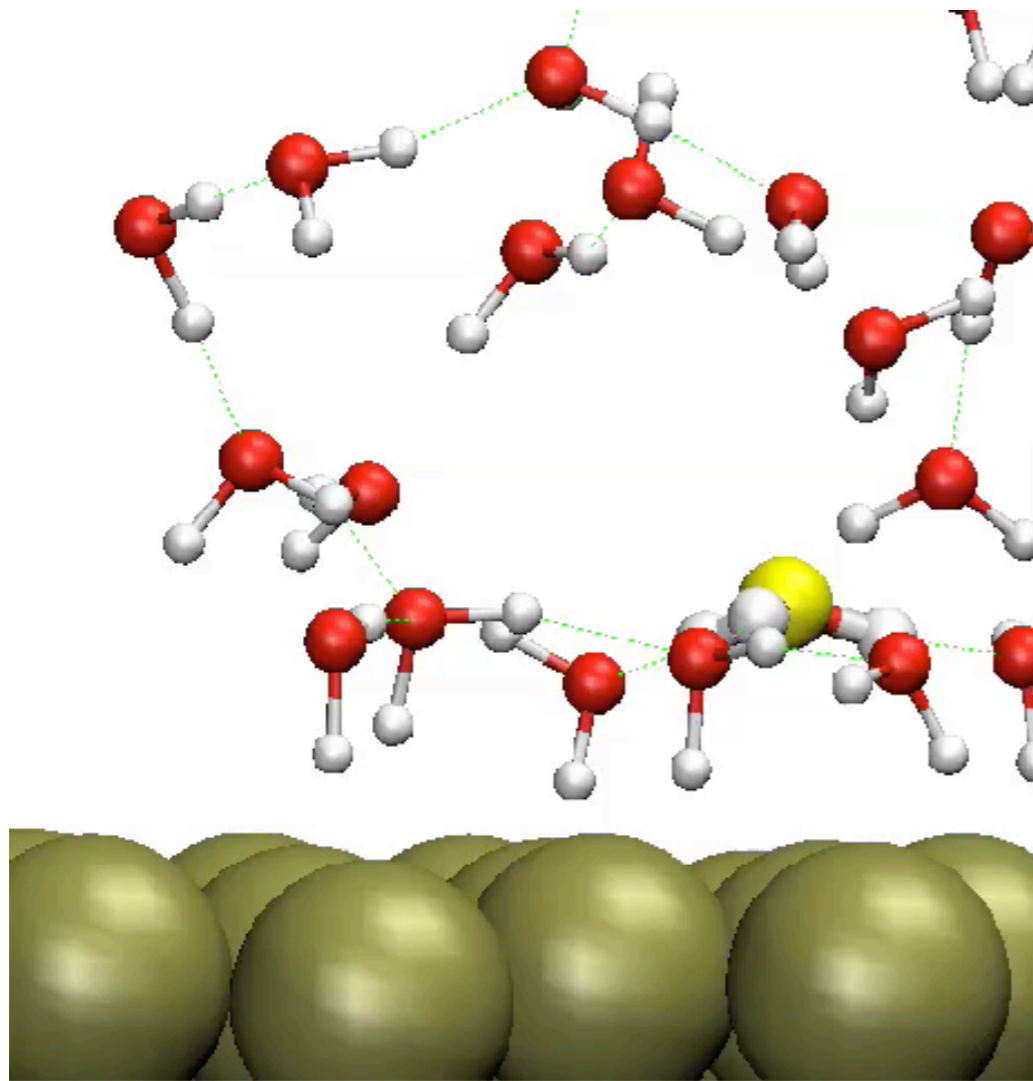


Outline

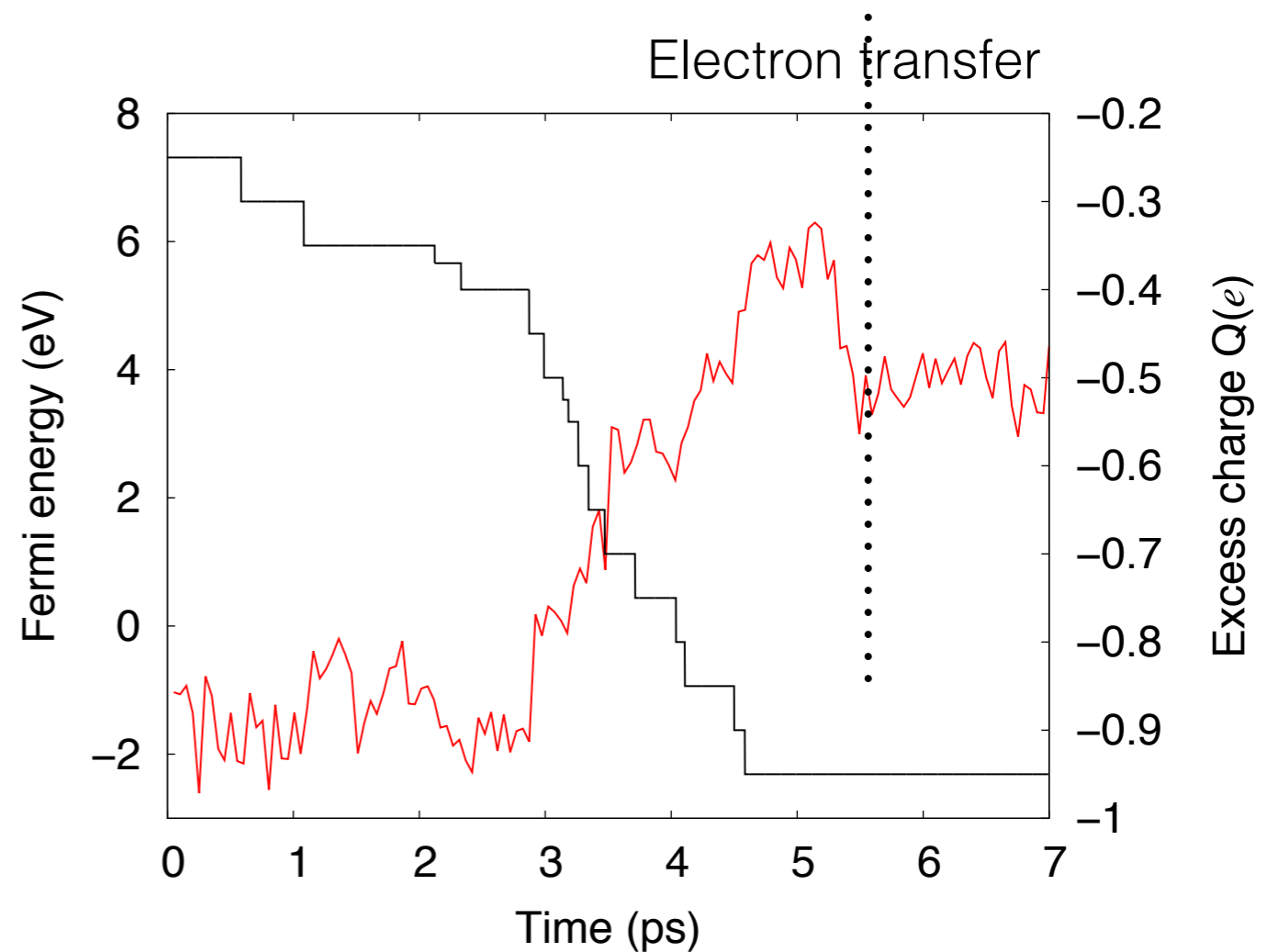
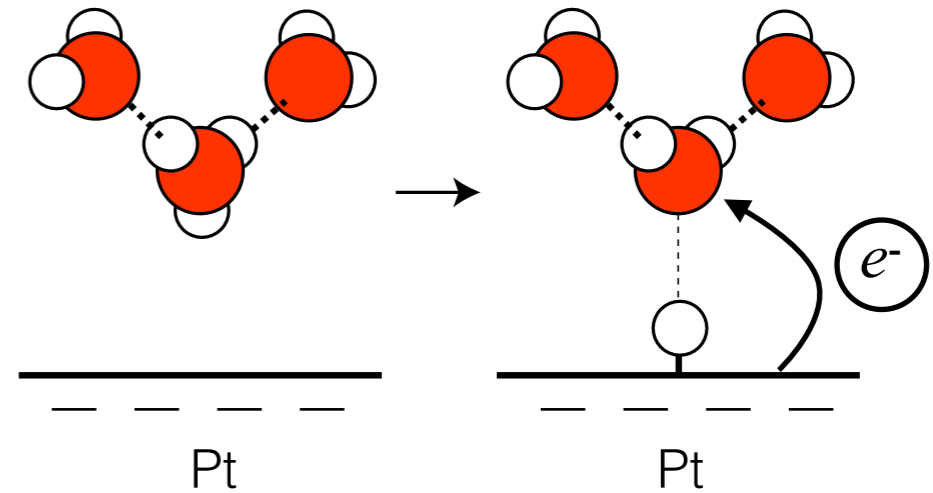
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Why we need a bias control?

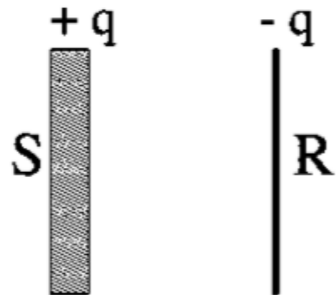

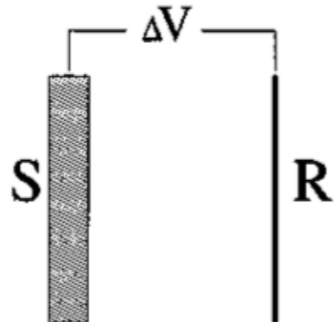

Hydrogen adsorption reaction



$Q = -0.95$ (e/cell)

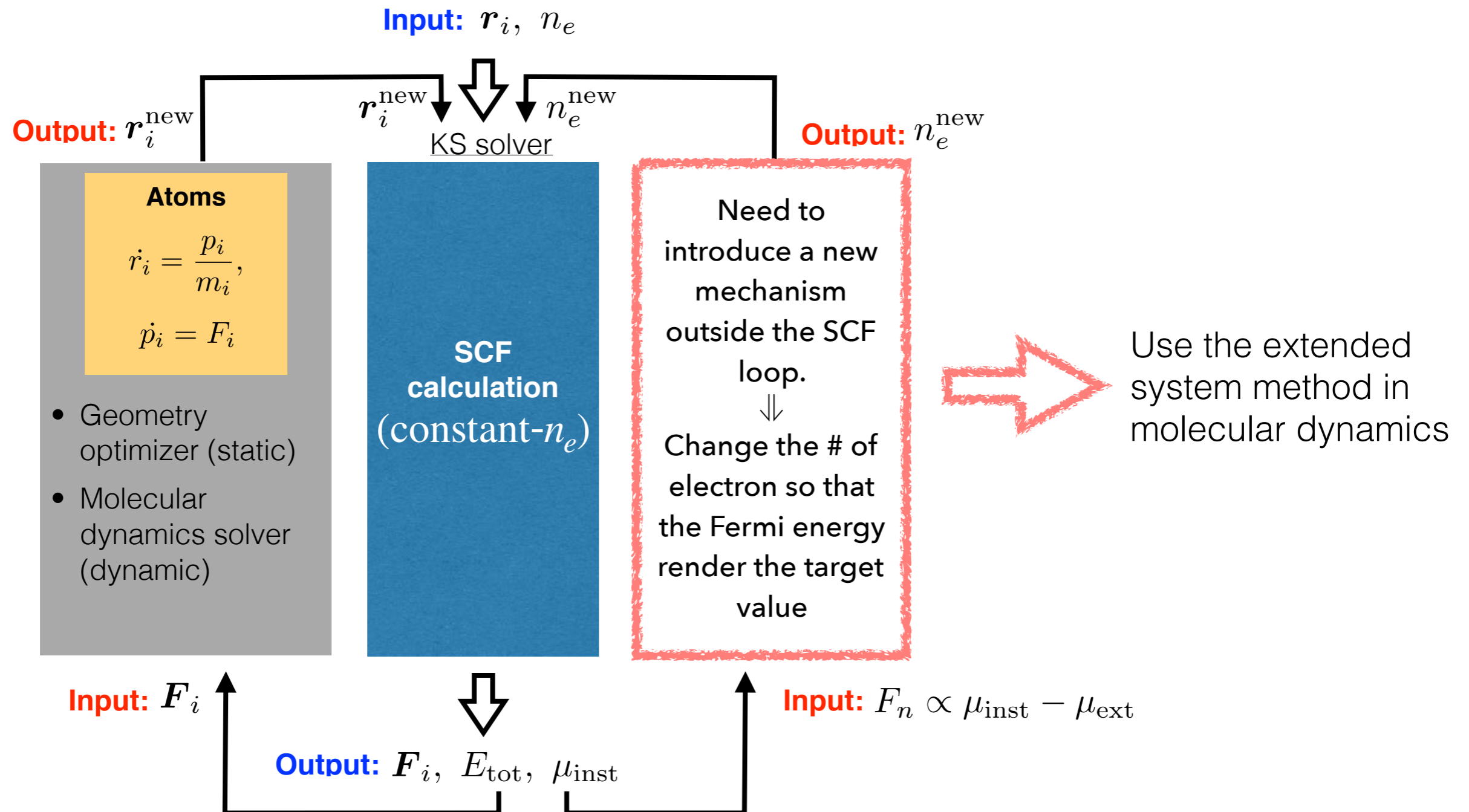


Limitation of the original conventional DFT-MD

Mode	Scheme	Thermodynamic potential	Experimental realization	
$N_e = \text{const}$		$F(T, V, N_e)$	Isolated capacitor	 conventional simulation
$\mu = \text{const}$		$\Omega(T, V, \mu)$	Electrochemistry (STM)	 experimental simulation

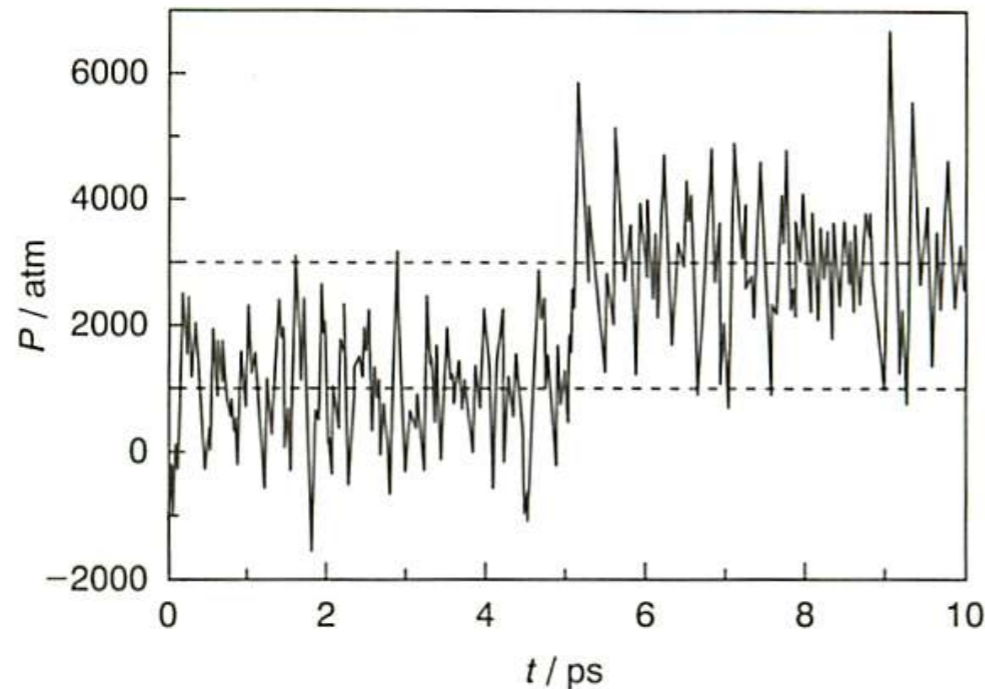
A. Lozovoi et al., JCP 115, 1661 (2001)

How to realize constant- μ_e system



Grand canonical ensemble in electronic system

Conventional **NPT** MD simulation



v_{cell} : Cell volume

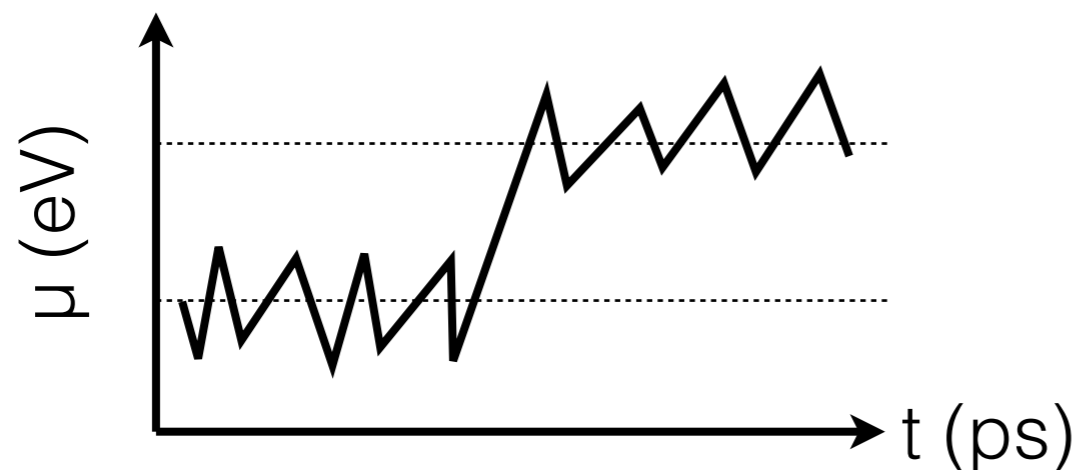
$M_{v_{\text{cell}}}$: Fictitious mass for variable cell

$$\dot{v}_{\text{cell}} = \frac{P_{v_{\text{cell}}}}{M_{v_{\text{cell}}}}$$

$$\dot{P}_{v_{\text{cell}}} = P - P_{\text{ext}}$$

from Virial theorem

If we can introduce a fictitious motion for amount of charge n_e , we can realize **NVT μ_e** MD simulation

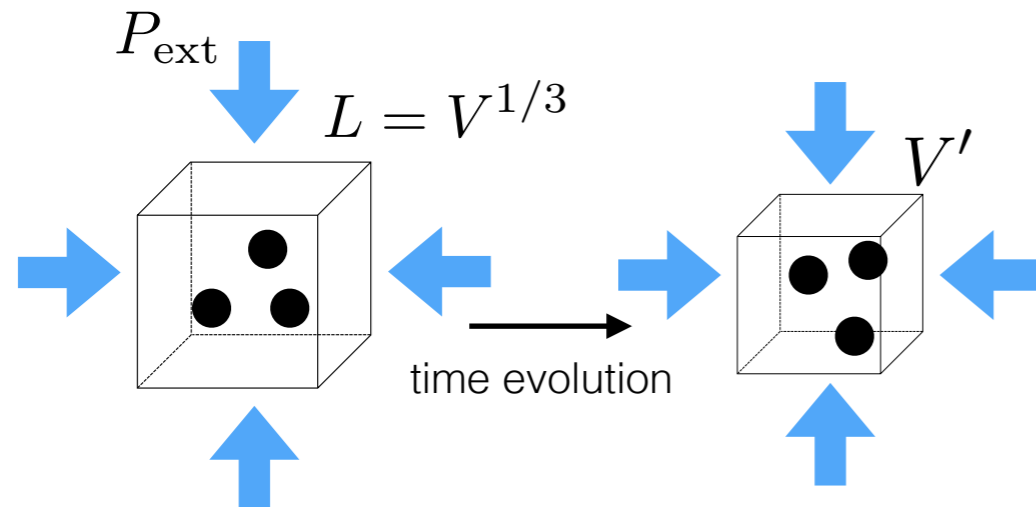


$$\dot{n}_{\text{cell}} = \frac{P_{n_{\text{cell}}}}{M_{n_{\text{cell}}}}$$

$$\dot{P}_{n_{\text{cell}}} = \mu - \mu_{\text{ext}}$$

Constant pressure MD (Andersen method)

H. C. Andersen, J. Chem. Phys. 72, 2384 (1980)



- Consider the volume as a dynamics variable
- Replace the coordinates \mathbf{r}_i by scaled coordinates $\tilde{\mathbf{r}}_i$,

$$\mathbf{r}_i = V^{\frac{1}{3}} \tilde{\mathbf{r}}_i, \quad (0 \leq \tilde{r}_i \leq 1)$$

and the time derivative of $\tilde{\mathbf{r}}_i$ is defined as

$$\dot{\mathbf{r}}_i = V^{\frac{1}{3}} \dot{\tilde{\mathbf{r}}}_i$$

Lagrangian for extended system

$$L_P = \frac{1}{2} \sum_i^N m_i V^{\frac{2}{3}} \dot{\tilde{\mathbf{r}}}_i^2 - E(\{V^{\frac{1}{3}} \tilde{\mathbf{r}}\}; \psi) + \frac{1}{2} W \dot{V}^2 - P_{\text{ext}} V$$

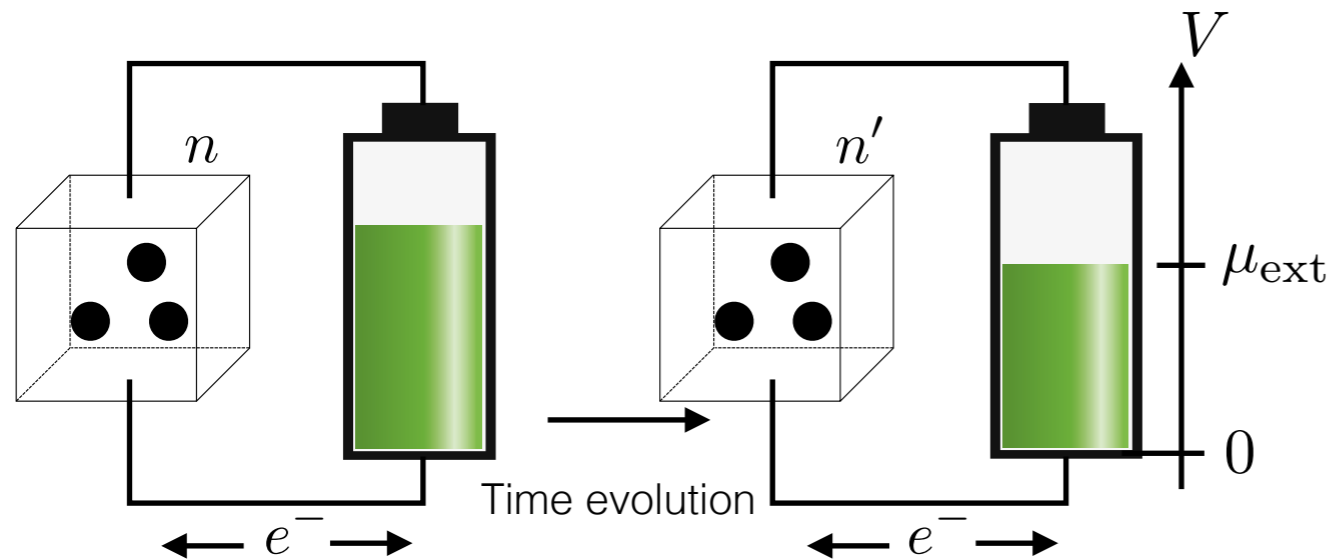
where, W is the fictitious mass of the cell. The Euler-Lagrange equation becomes

$$\left\{ \begin{array}{l} m_i \ddot{\tilde{\mathbf{r}}}_i = -V^{-\frac{2}{3}} \frac{\partial E(\{V^{\frac{1}{3}} \tilde{\mathbf{r}}\}; \psi)}{\partial \tilde{\mathbf{r}}_i} - \frac{2\dot{V}}{3V} \dot{\tilde{\mathbf{r}}}_i \\ W \ddot{V} = \frac{1}{3V} \left[\sum_i^N m_i V^{\frac{2}{3}} \dot{\tilde{\mathbf{r}}}_i^2 - \sum_i^N \mathbf{r}_i \cdot \frac{\partial E(\{\mathbf{r}\}; \psi)}{\partial \mathbf{r}_i} \right] - P_{\text{ext}} \end{array} \right.$$

Instantaneous pressure
(Virial theorem)

Constant- μ MD

N. Bonnet et al., Phys. Rev. Lett. 109, 266101 (2012)



- Consider FCP as a dynamical variable
- Connecting the system to a potentiostat to keep the Fermi energy of the system as target Fermi energy μ_{ext} .

Lagrangian for extended system

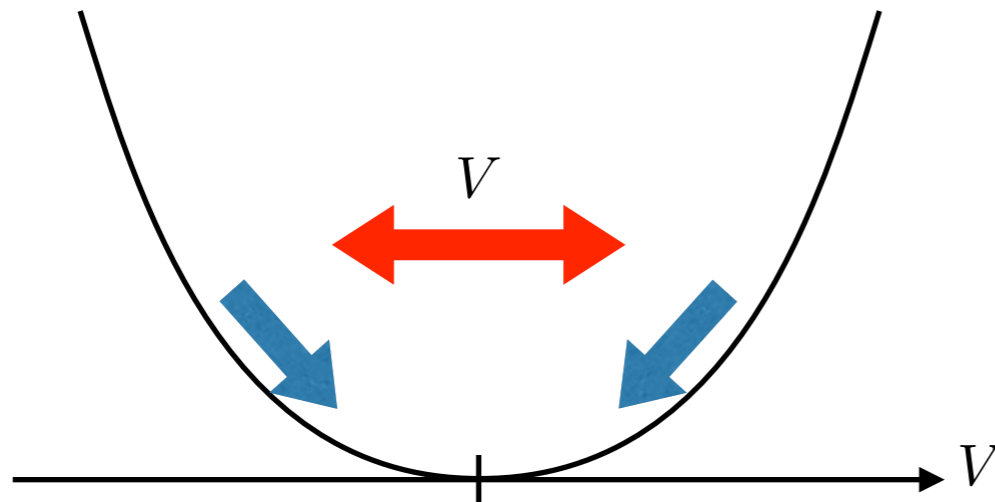
$$L_{\mu} = \frac{1}{2} \sum_i^N m_i \dot{\mathbf{r}}_i^2 - E(\{\mathbf{r}\}; \psi) + \frac{1}{2} M \dot{n}^2 - (-\mu_{\text{ext}} n)$$

where, M is the fictitious mass of FCP. The Euler-Lagrange equation becomes

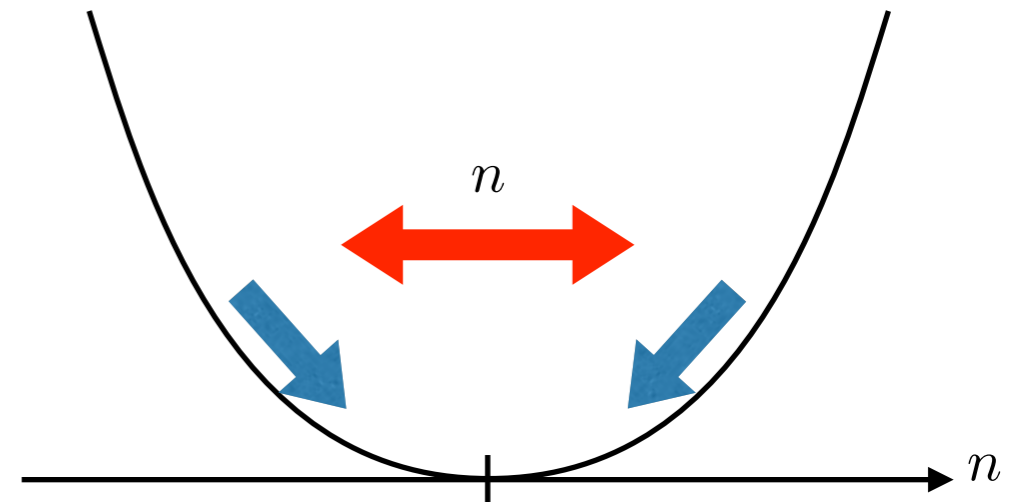
$$\begin{cases} m_i \ddot{\mathbf{r}}_i = - \frac{\partial E(\{\mathbf{r}_i\}; \psi)}{\partial \mathbf{r}_i} \\ M \ddot{n} = - \left(\frac{\partial E(\{\mathbf{r}_i\}; \psi)}{\partial n} - \mu_{\text{ext}} \right) \end{cases}$$

Instantaneous Fermi energy

Constant pressure



Constant chemical potential



Extensive var.

$$-\delta V \quad V_0 \quad \delta V$$



Intensive var.

$$P_{\text{in}} > P_{\text{ext}} \quad P_{\text{in}} = P_{\text{ext}} \quad P_{\text{in}} < P_{\text{ext}}$$

$$-\delta n \quad n_0 \quad \delta n$$



$$\mu_{\text{in}} < \mu_{\text{ext}} \quad \mu_{\text{in}} = \mu_{\text{ext}} \quad \mu_{\text{in}} > \mu_{\text{ext}}$$

Mean value

$$P_{\text{ext}} = \langle P_{\text{in}} \rangle$$

$$\mu_{\text{ext}} = \langle \mu_{\text{in}} \rangle$$

Linearization
at equilibrium

$$W\ddot{V} = P_{\text{in}} - P_{\text{ext}}$$

$$\rightarrow W\delta\ddot{V} \simeq -\frac{B}{V_0}\delta V$$

$$M\ddot{n} = \mu_{\text{in}} - \mu_{\text{ext}}$$

$$\rightarrow M\delta\ddot{n} \simeq -\frac{1}{C}\delta n$$

Restoring force yields the oscillation around the bottom

$$\text{Bulk modulus: } B = -V_0 \frac{\partial P}{\partial V}$$

$$\text{Capacitance: } \frac{1}{C} = \frac{\partial \mu}{\partial n}$$

Statistical ensemble

By connecting an appropriate thermostat, e.g. Nosé thermostat, scaling method..., we can realize an isobaric and grand canonical ensembles.

Isobaric

Grand canonical (for electron)

Partition function

$$Y = \iiint \exp [-(\mathcal{H} + P_{\text{ext}}V)/k_B T] d\mathbf{r}d\mathbf{q}dV \quad \Xi_\mu = \iiint \exp [-(\mathcal{H} - \mu_{\text{ext}}n)/k_B T] d\mathbf{r}d\mathbf{q}dn$$

$$\mathcal{H} = \frac{1}{2} \sum_i^N m_i \mathbf{r}_i^2 + E(\{\mathbf{r}\}; \psi) \quad \mathcal{H} = \frac{1}{2} \sum_i^N m_i \mathbf{r}_i^2 + E(\{\mathbf{r}\}; \psi)$$

Compressibility

Capacitance

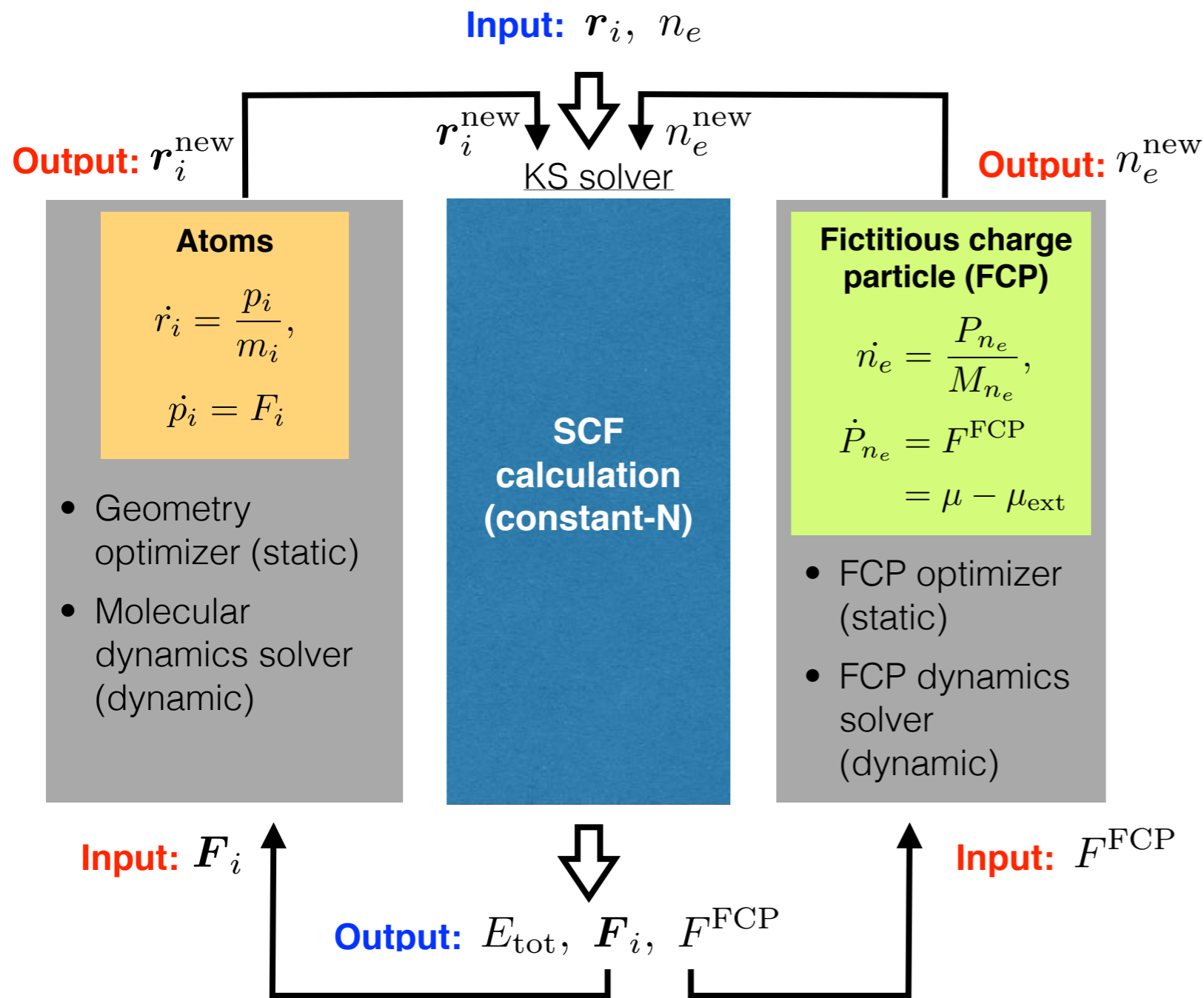
Fluctuation of extensive variable

$$\kappa = -\frac{1}{\langle V \rangle} \frac{\partial \langle V \rangle}{\partial P_{\text{ext}}} = \frac{\langle \delta V^2 \rangle}{k_B T \langle V \rangle}$$

$$C = \frac{\partial \langle n \rangle}{\partial \mu_{\text{ext}}} = \frac{\langle \delta n^2 \rangle}{k_B T}$$

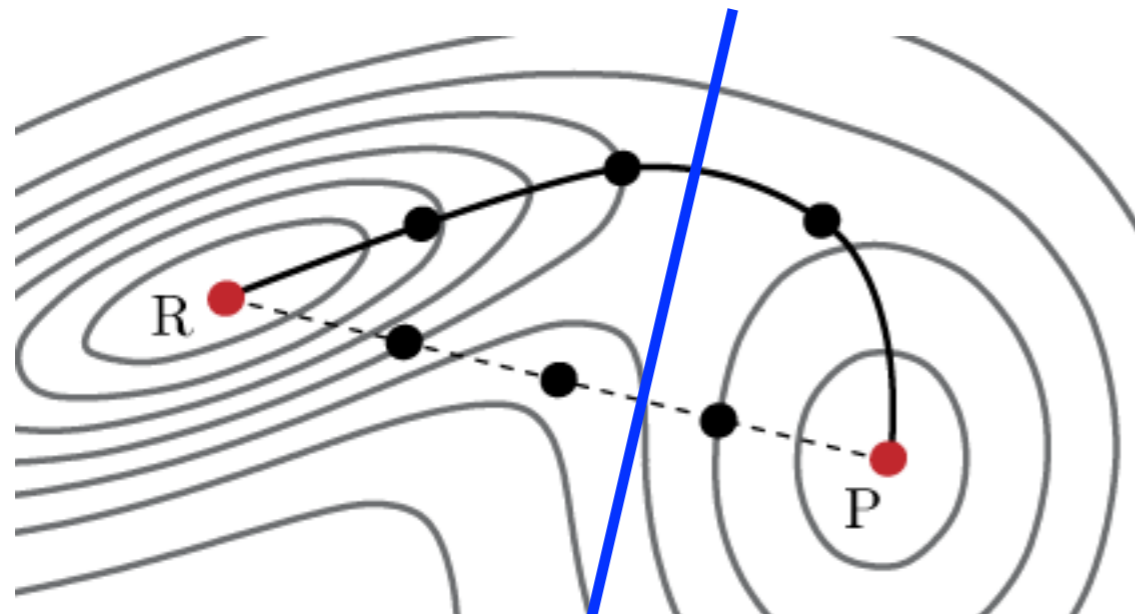
Johnson-Nyquist noise

How to realize constant- μ system



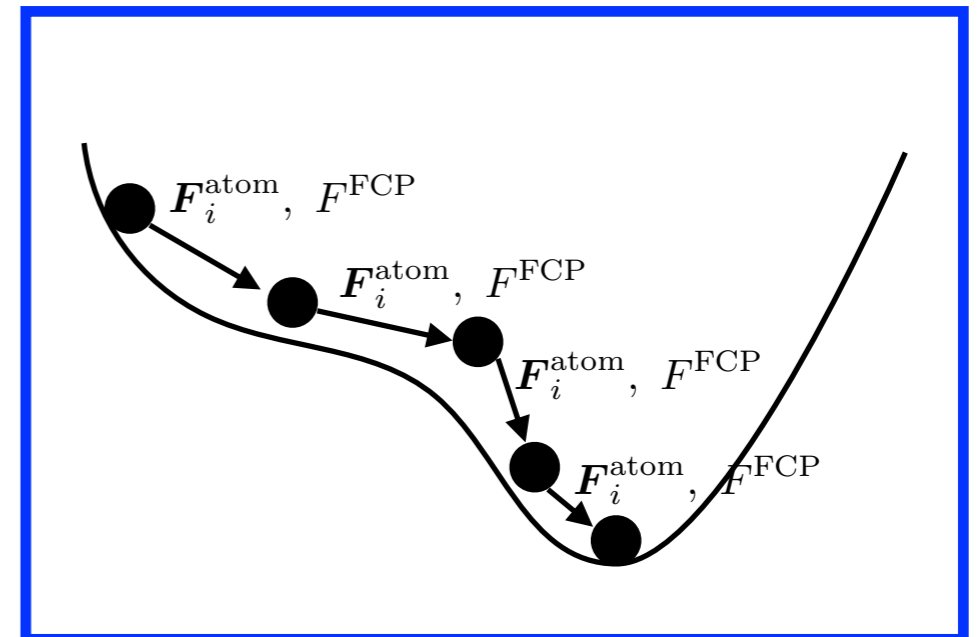
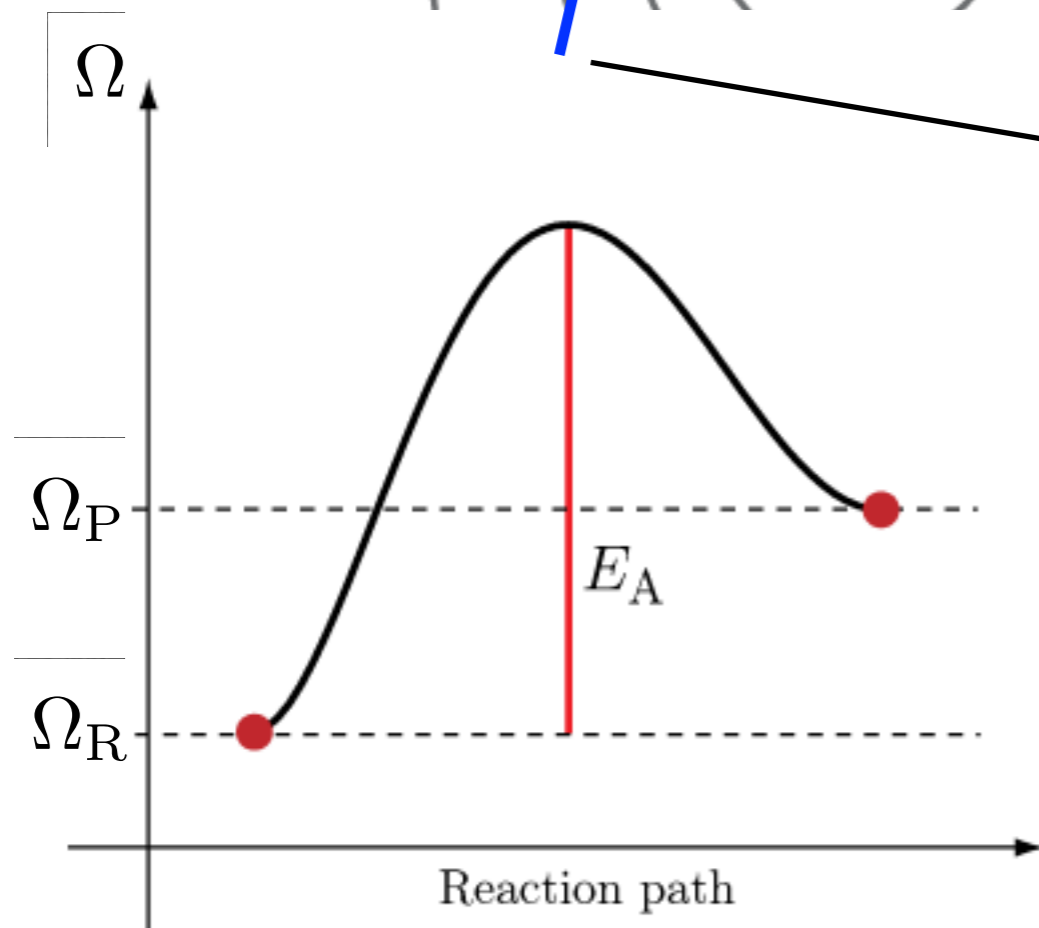
- Fictitious charge particle (FCP) is introduced with fictitious mass.
- For static calculation, FCP is optimized by line minimization scheme. We can obtain the grand potential.
- For MD simulation, FCP is evolved by equation of motion for FCP. We can obtain the grand canonical ensemble.
- FCP is updated at each atomic step. (e.g., Geometry optimization step, MD step)

NEB method in Ω -space



Searching the minimum energy path (MEP) using NEB with constant- μ

Constrained geometry optimisation on hyperplane in \tilde{E} -space



FCP is also updated at each atomic step.
 \Rightarrow no additional calculation cost

Generalized force acting on atoms & FCP

Minimize Ω instead of the total energy E

$$\Omega = E - \mu_{\text{ext}}n$$

\tilde{E} includes the potential $\mu_{\text{ext}}n$ derived from an external potentiostat.
Force acting on atoms

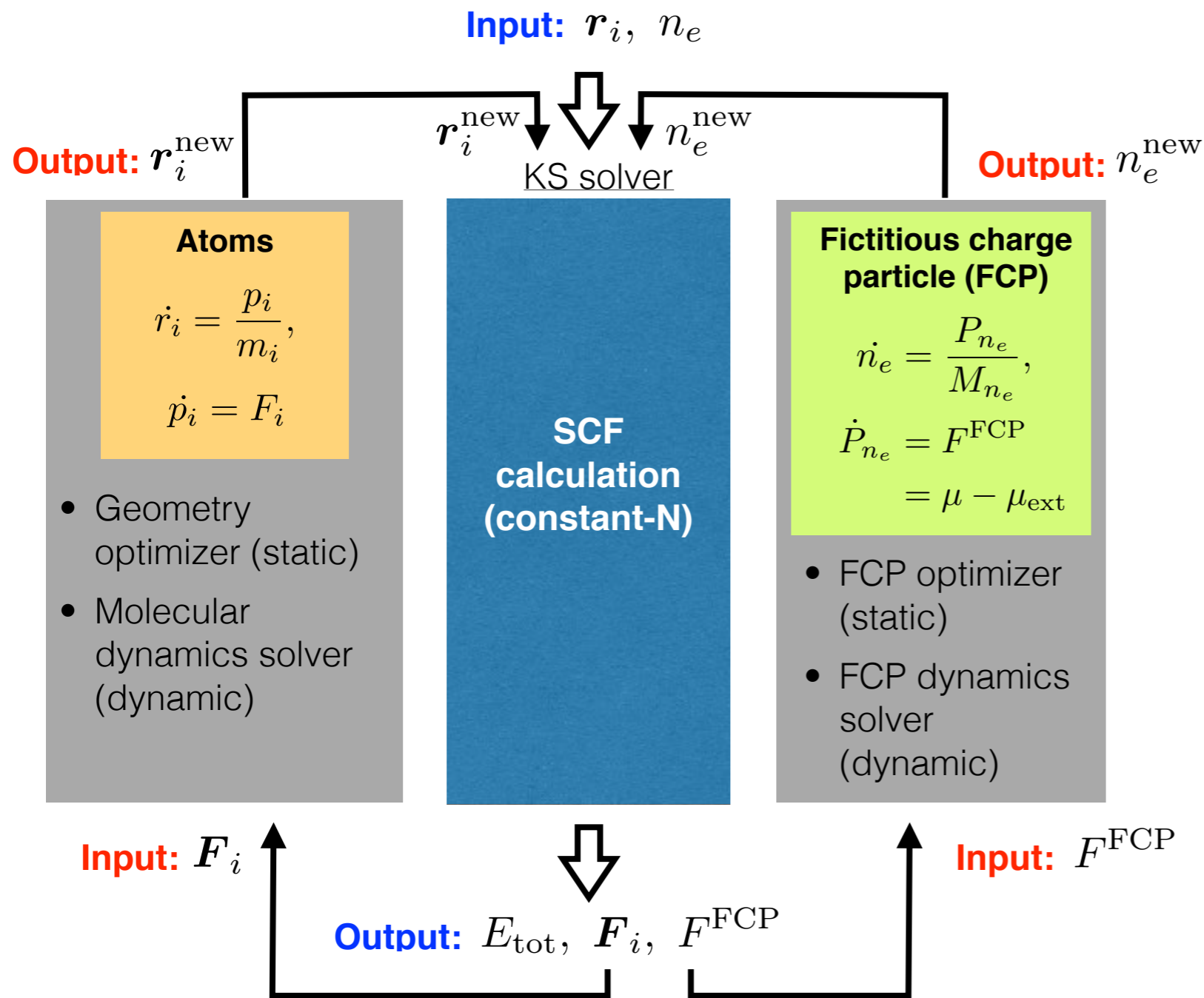
$$\mathbf{F}_i = -\frac{\partial \Omega}{\partial \mathbf{r}_i} = -\frac{\partial E}{\partial \mathbf{r}_i}$$

Force acting on FCP

$$F^{\text{FCP}} = -\frac{\partial \Omega}{\partial n} = -(\mu - \mu_{\text{ext}})$$

We need to consider the generalized force acting on atoms & FCP to optimize the geometry and μ .

How to realize constant- μ system



- Fictitious charge particle (FCP) is introduced with fictitious mass.
- For static calculation, FCP is optimized by line minimization scheme. We can obtain the grand potential.
- For MD simulation, FCP is evolved by equation of motion for FCP. We can obtain the grand canonical ensemble.
- FCP is updated at each atomic step. (e.g., Geometry optimization step, MD step)

Test calculation (Pt-H₂O interface)

constant-N

$$T_{\text{atom}} = 353 \text{ K}$$

$$Q = 0.35 \text{ (e/cell)}$$

constant- μ

$$\mu_{\text{ext}} = -6.0 \text{ eV}$$

$$T = 300 \text{ K}$$

$$M_{n_e} = 300 \text{ cm}^{-1}$$

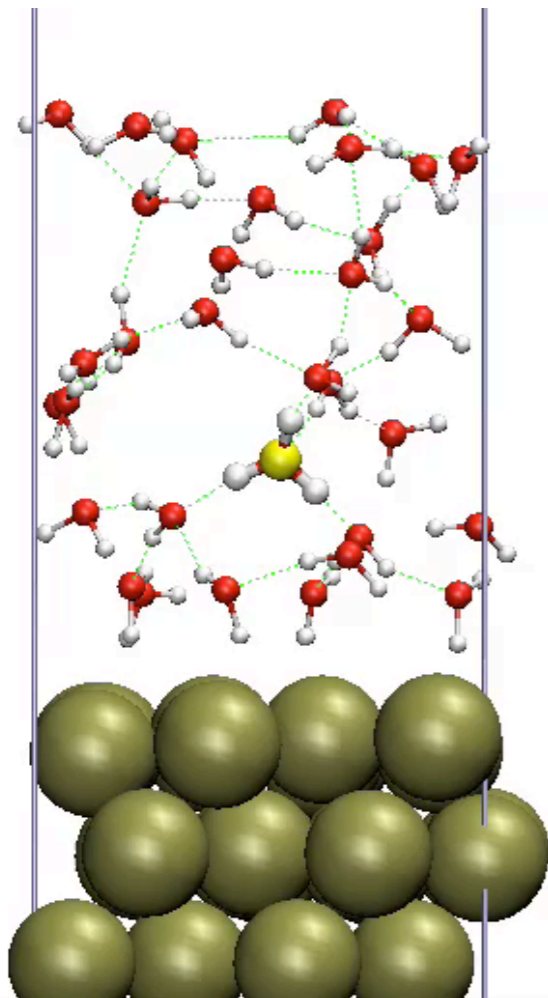
$$M_{\xi_e} = 100 \text{ cm}^{-1}$$

$$\mu_{\text{ext}} = -4.9 \text{ eV}$$

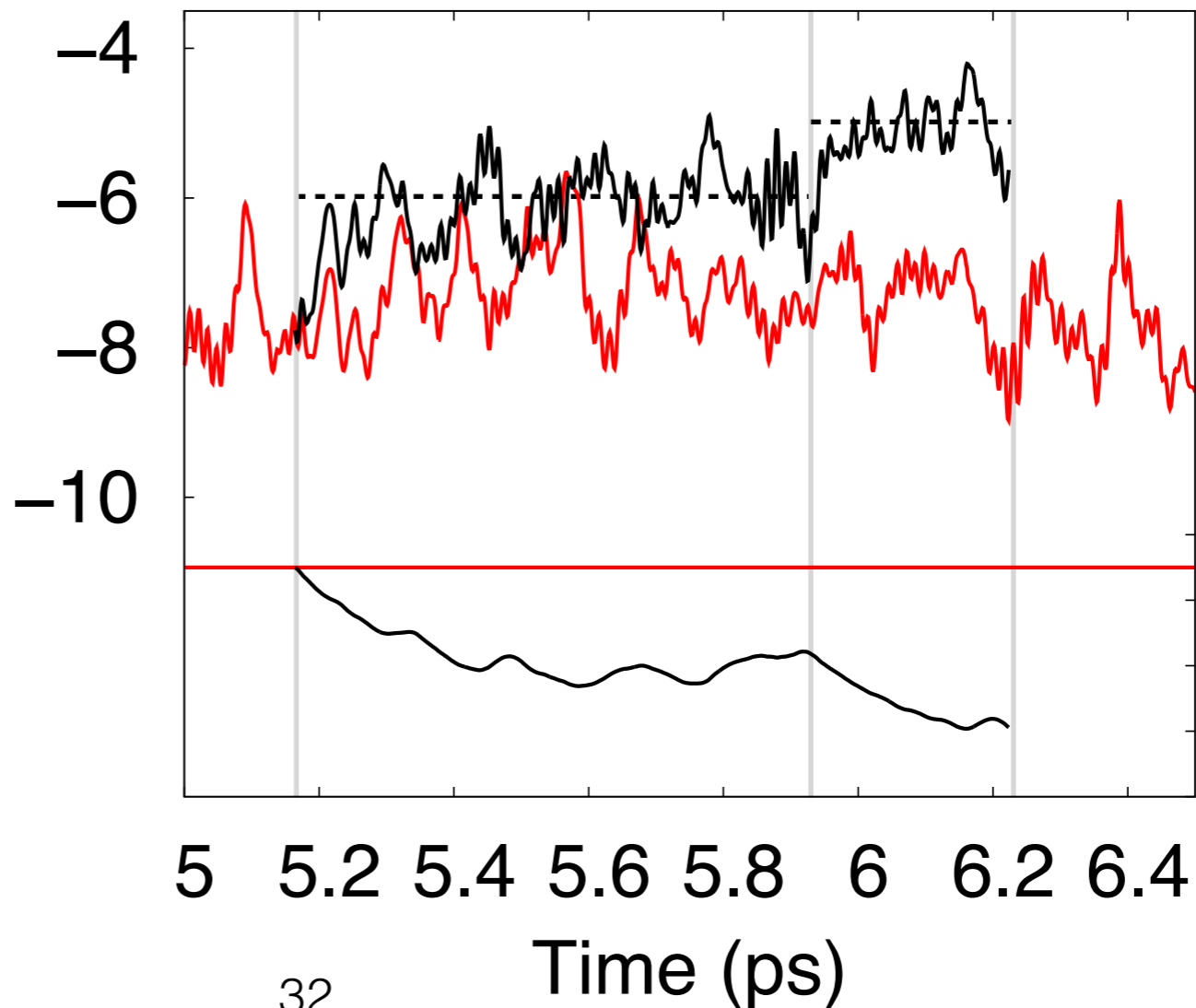
$$T = 300 \text{ K}$$

$$M_{n_e} = 300 \text{ cm}^{-1}$$

$$M_{\xi_e} = 100 \text{ cm}^{-1}$$



Fermi energy (eV)



Excess charge $Q(e)$

Outline

- Introduction
- Simulation platform for electrochemical interface
 - Effective screening medium (**ESM**) method
 - Constant bias potential (**constant- μ_e**) method
 - Hybrid simulation method: DFT+liquid theory (**ESM-RISM**)
- Applications
 - Lithium Insertion/Desorption Reaction in Li-ion battery
- Summary
- Appendix (How to define the electrode potential from DFT)

Simulation platform for electrochemical interfaces

1. Strong electric field in Helmholtz layer

ESM method

Effective Screening Medium method
Phys. Rev. B **73**, 115407 (2006)

2. Bias potential control

Constant- μ method

Phys. Rev. Lett. **109**, 266101 (2012)

3. Screening in diffuse layer

ESM-RISM method

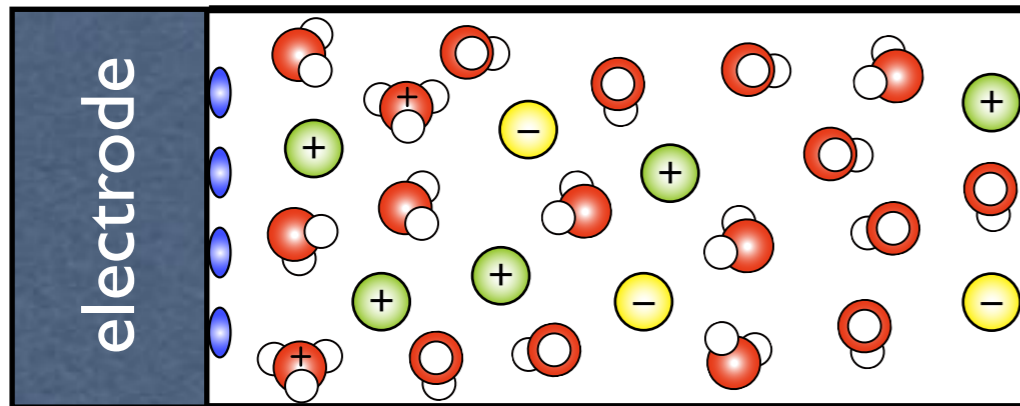
Reference Interaction Site Model

4. Origin of electrostatic potential

Phys. Rev. B **96**, 115429 (2017)

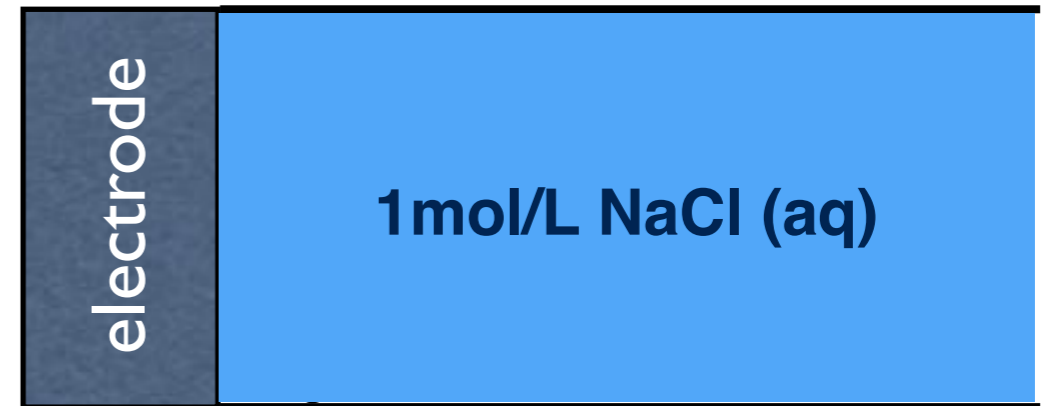
Simulation platform for electrochemical interfaces

- Explicit solvation model



- All atom calculation
- BOMD, CPMD, ...

- Implicit solvation model



- Classical liquid theory
- JDFTx, ENVIRON, PCM, ...

3. Screening in diffuse layer

4. Origin of electrostatic potential

ESM-RISM method

Reference Interaction Site Model

Phys. Rev. B **96**, 115429 (2017)

Concept of DFT+continuum medium hybrid method

Total energy functional

$$E[\rho] = T[\rho] + E_{\text{xc}}[\rho] + \frac{1}{2} \iint d\mathbf{r} d\mathbf{r}' \frac{\rho(\mathbf{r})\rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} + \int d\mathbf{r} v_{\text{ext}}(\mathbf{r})\rho(\mathbf{r}) + E_{\text{ion}}$$

$V \rightsquigarrow$ variable

$$E[\rho_e, V] = T[\rho_e] + E_{\text{xc}}[\rho_e] + \int d\mathbf{r} \left[+\frac{\epsilon(\mathbf{r})}{8\pi} |\nabla V(\mathbf{r})|^2 + \rho_{\text{tot}}(\mathbf{r})V(\mathbf{r}) \right]$$

$$\frac{\delta E}{\delta V} = 0$$

Generalized Poisson equation

$$\nabla[\epsilon(\mathbf{r})\nabla]V(\mathbf{r}) = -4\pi\rho_{\text{tot}}(\mathbf{r}) \longleftarrow \rho_{\text{tot}} = \rho_{\text{DFT}} + \rho_{\text{solv}}$$

$$\frac{\delta E}{\delta \rho_e} = 0$$

Kohn-Sham equation

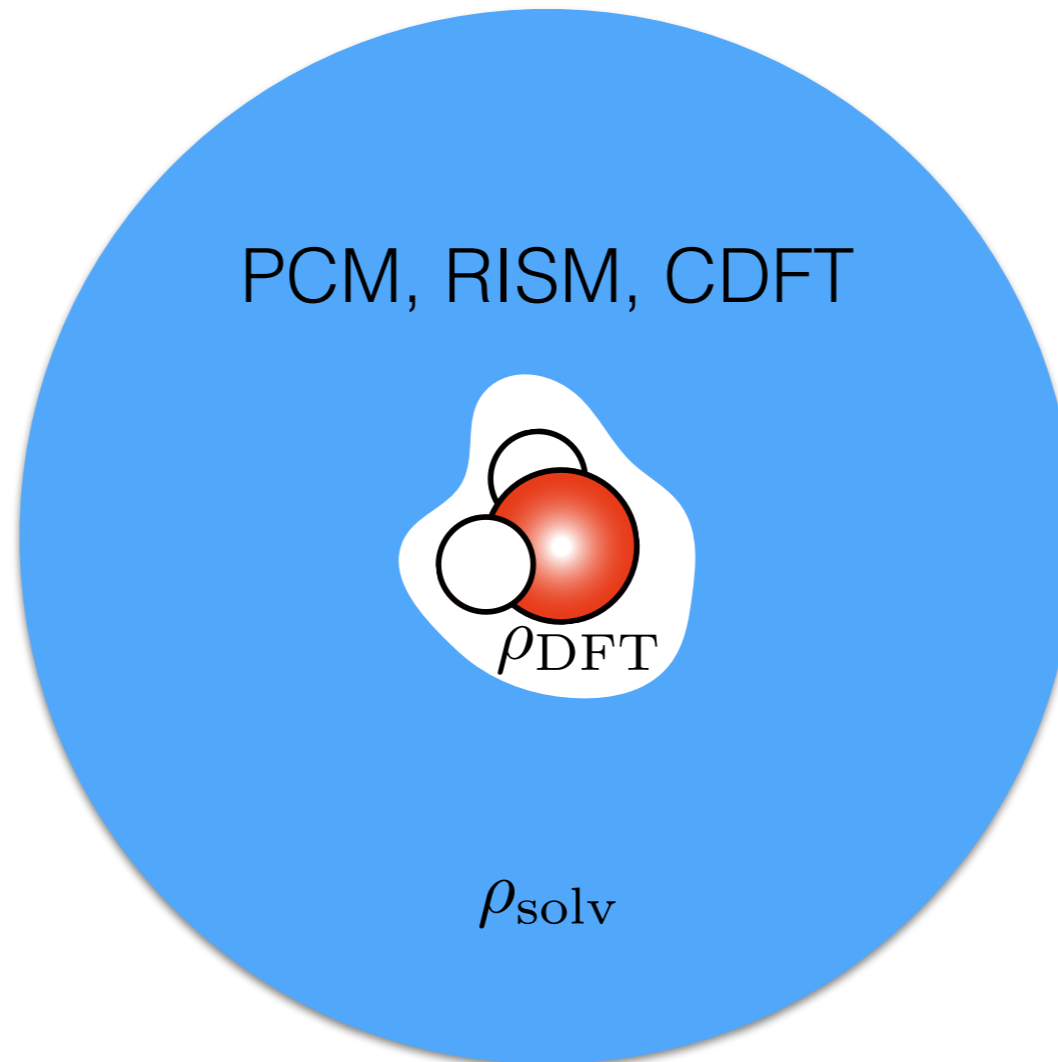
$$\left[-\frac{1}{2}\nabla^2 + V(\mathbf{r}) + \hat{V}_{\text{NL}} + V_{\text{xc}}(\mathbf{r}) \right] \psi_i(\mathbf{r}) = \epsilon_i \psi_i(\mathbf{r})$$

PCM: Environ
RISM: ESM-RISM
CDFT: JDFT

Concept of DFT+continuum medium hybrid method

Generalized Poisson equation

$$\nabla[\epsilon(\mathbf{r})\nabla]V(\mathbf{r}) = -4\pi\rho_{\text{tot}}(\mathbf{r}) \longleftarrow \rho_{\text{tot}} = \rho_{\text{DFT}} + \rho_{\text{solv}}$$



Concept of DFT+continuum medium hybrid method

Generalized Poisson equation

$$\nabla[\epsilon(\mathbf{r})\nabla]V(\mathbf{r}) = -4\pi\rho_{\text{tot}}(\mathbf{r}) \longleftarrow \rho_{\text{tot}} = \rho_{\text{DFT}} + \rho_{\text{solv}}$$

PCM, JDFT

$$\epsilon(\mathbf{r}) = 1$$

$$V(\mathbf{r}) = \int d\mathbf{r}' \frac{\rho_{\text{tot}}(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|}$$

ESM

$\epsilon(\mathbf{r})$: model dependent

$$V(\mathbf{r}) = \int d\mathbf{r}' G^{\text{MBC}}(\mathbf{r}, \mathbf{r}') \rho_{\text{tot}}(\mathbf{r}')$$

Laue representation

$$\left[\partial_z \{ \epsilon(z) \partial_z \} - \epsilon(z) g_{\parallel}^2 \right] V(\mathbf{g}_{\parallel}, z) = -4\pi \rho_{\text{tot}}(\mathbf{g}_{\parallel}, z)$$

Open boundary condition

$$\partial_z V(\mathbf{g}_{\parallel}, z) \Big|_{z=\pm\infty} = 0, \quad \epsilon(z) = 1$$

$$\begin{cases} G^{\text{MBC}}(\mathbf{g}_{\parallel}, z, z') = \frac{4\pi}{2g_{\parallel}} e^{-g_{\parallel}|z-z'|} \\ G^{\text{MBC}}(\mathbf{r}_{\parallel} - \mathbf{r}'_{\parallel}, z, z') = \frac{1}{\sqrt{|\mathbf{r}_{\parallel} - \mathbf{r}'_{\parallel}|^2 + (z - z')^2}} \end{cases}$$

Concept of DFT+continuum medium hybrid method

Total energy functional

$$E[\rho] = T[\rho] + E_{\text{xc}}[\rho] + \frac{1}{2} \iint d\mathbf{r} d\mathbf{r}' \frac{\rho(\mathbf{r})\rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} + \int d\mathbf{r} v_{\text{ext}}(\mathbf{r})\rho(\mathbf{r}) + E_{\text{ion}}$$

$V \rightsquigarrow$ variable

$$E[\rho_e, V] = T[\rho_e] + E_{\text{xc}}[\rho_e] + \int d\mathbf{r} \left[+\frac{\epsilon(\mathbf{r})}{8\pi} |\nabla V(\mathbf{r})|^2 + \rho_{\text{tot}}(\mathbf{r})V(\mathbf{r}) \right]$$

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PCM, JDFT

$$\epsilon(\mathbf{r}) = 1$$

$$V(\mathbf{r}) = \int d\mathbf{r}' \frac{\rho_{\text{tot}}(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|}$$

$$\frac{\delta E}{\delta \rho_e} = 0$$

Kohn-Sham equation

$$\left[-\frac{1}{2}\nabla^2 + V(\mathbf{r}) + \hat{V}_{\text{NL}} + V_{\text{xc}}(\mathbf{r}) \right] \psi_i(\mathbf{r}) = \epsilon_i \psi_i(\mathbf{r})$$

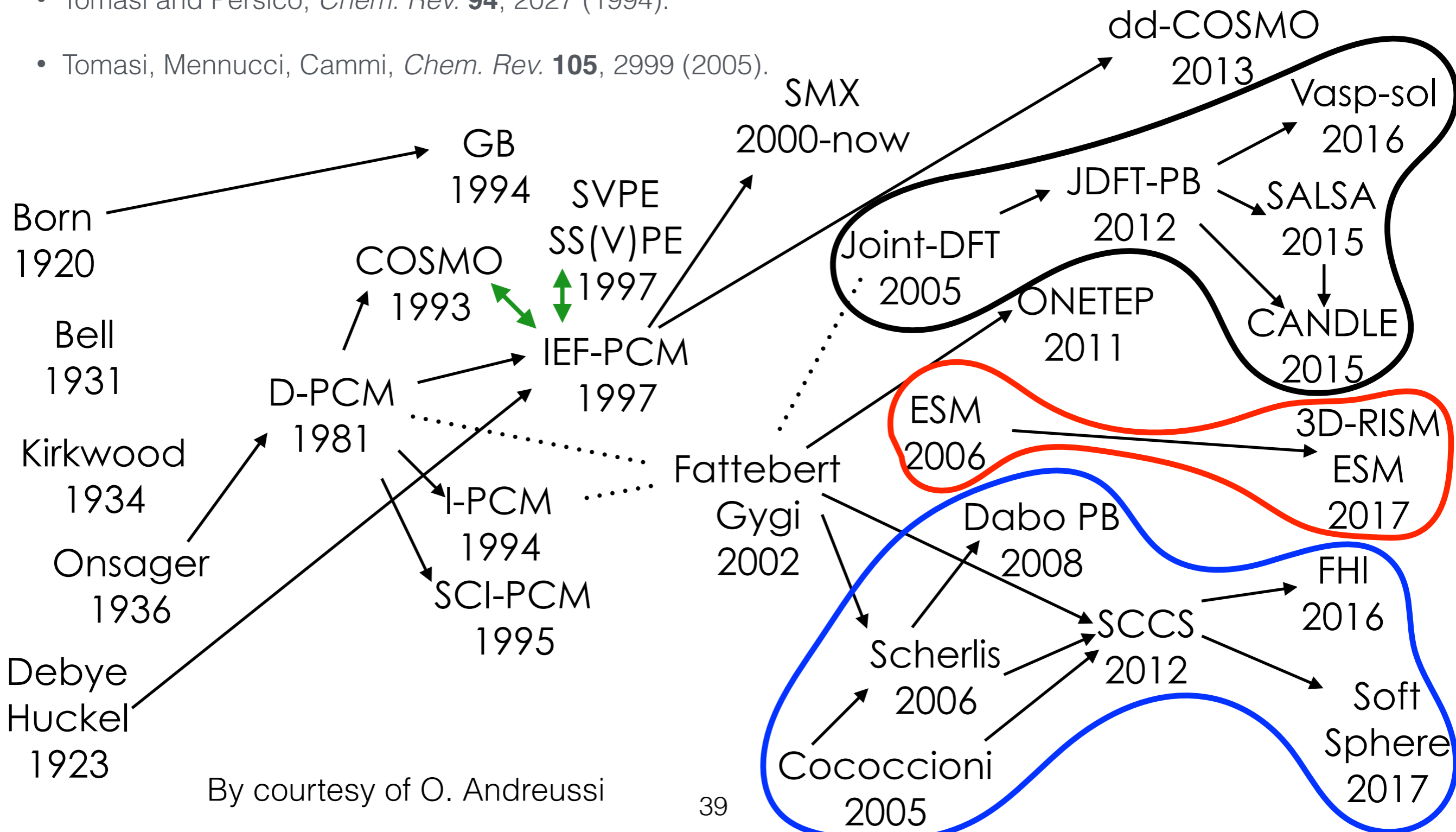
ESM

$\epsilon(\mathbf{r})$: model dependent

$$V(\mathbf{r}) = \int d\mathbf{r}' G^{\text{MBC}}(\mathbf{r}, \mathbf{r}')\rho_{\text{tot}}(\mathbf{r}')$$

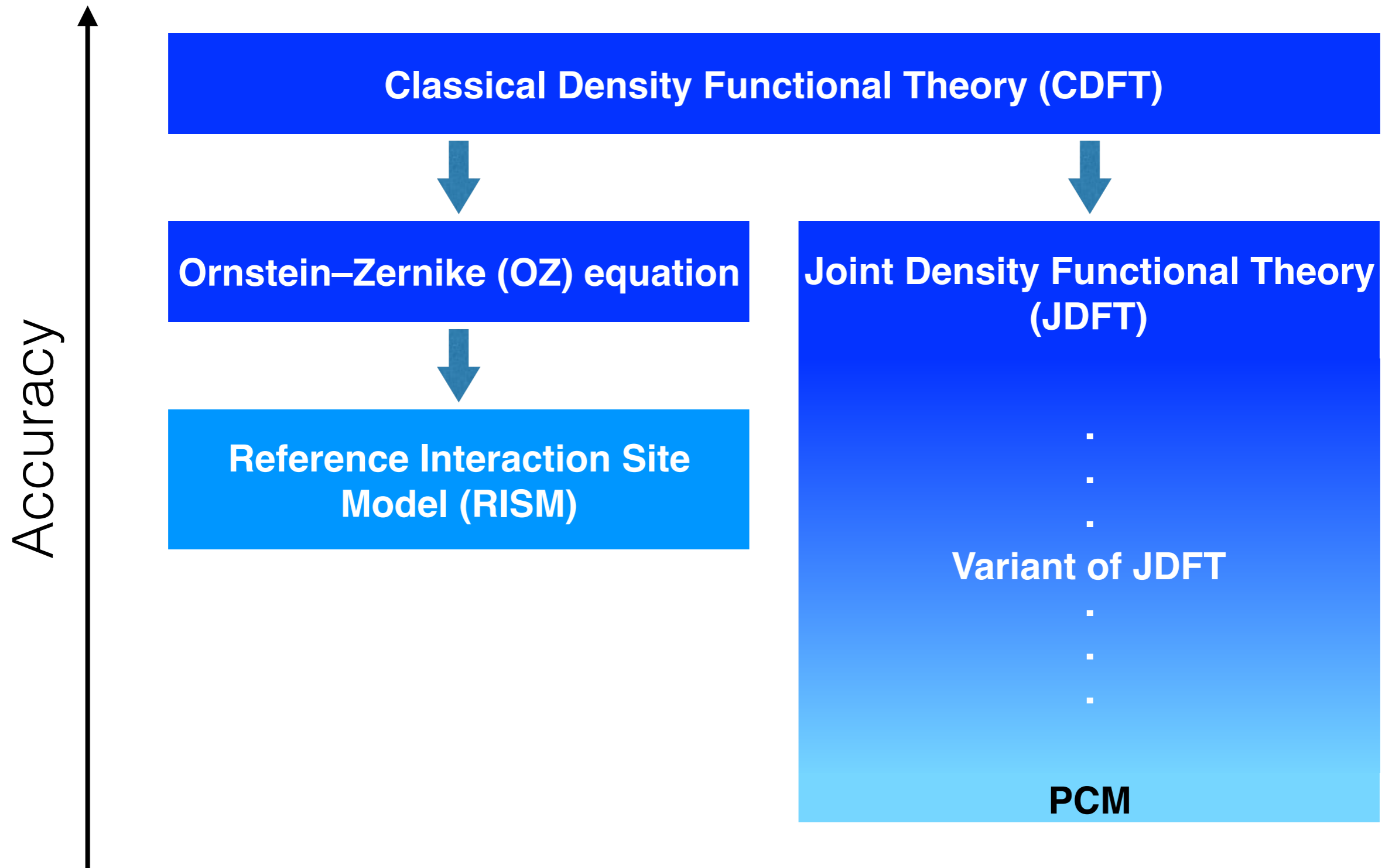
Continuum Genealogy

- Tomasi and Persico, *Chem. Rev.* **94**, 2027 (1994).
- Tomasi, Mennucci, Cammi, *Chem. Rev.* **105**, 2999 (2005).



By courtesy of O. Andreussi

Implicit solvation models



What is the RISM theory?

Ornstein-Zernike equation

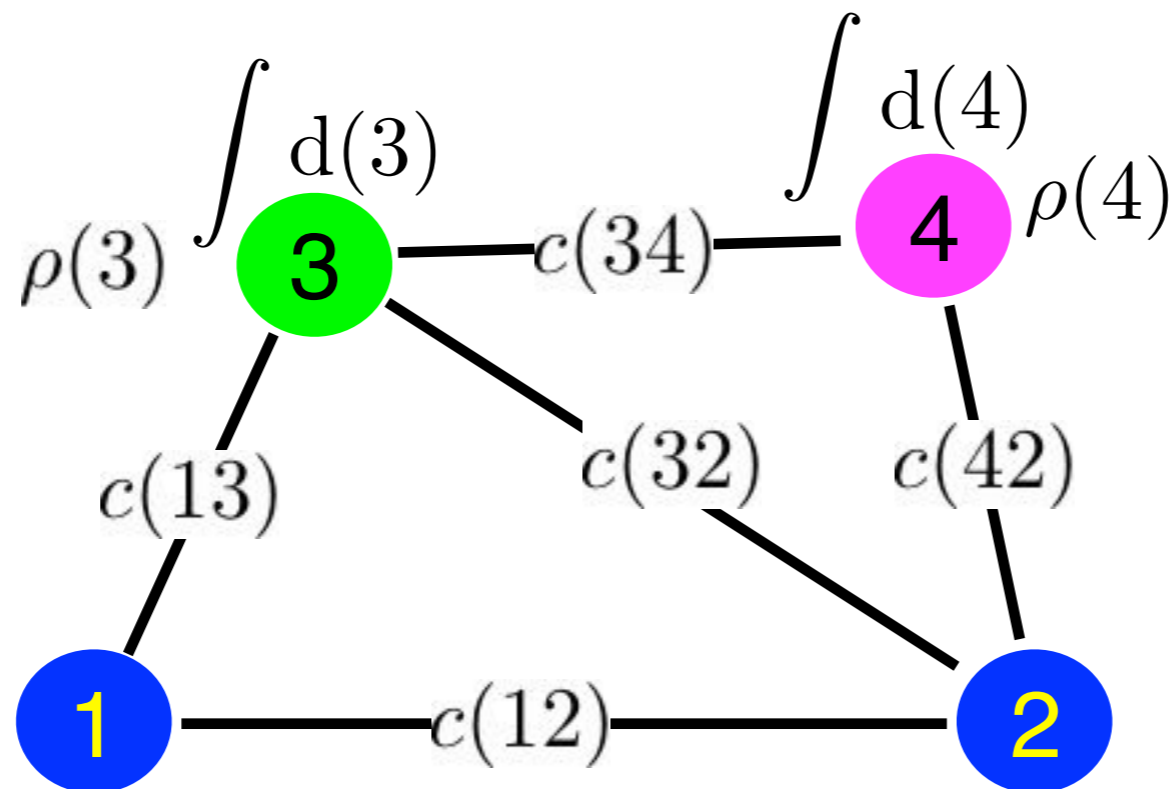
$$\begin{cases} h(\mathbf{r}_1, \mathbf{r}_2) = c(\mathbf{r}_1, \mathbf{r}_2) + \int d\mathbf{r}_3 c(\mathbf{r}_1, \mathbf{r}_3) \rho(\mathbf{r}_3) h(\mathbf{r}_3, \mathbf{r}_2) \\ h(\mathbf{r}_1, \mathbf{r}_2) = g(\mathbf{r}_1, \mathbf{r}_2) - 1 \end{cases}$$

Direct correlation function

Total correlation function

Pair distribution function

$$h(12) = c(12) + \int d(3) c(13) \rho(3) c(32) + \int d(3) d(4) c(13) \rho(3) c(34) \rho(4) c(42) \dots$$



1D-RISM

1D-RISM equation

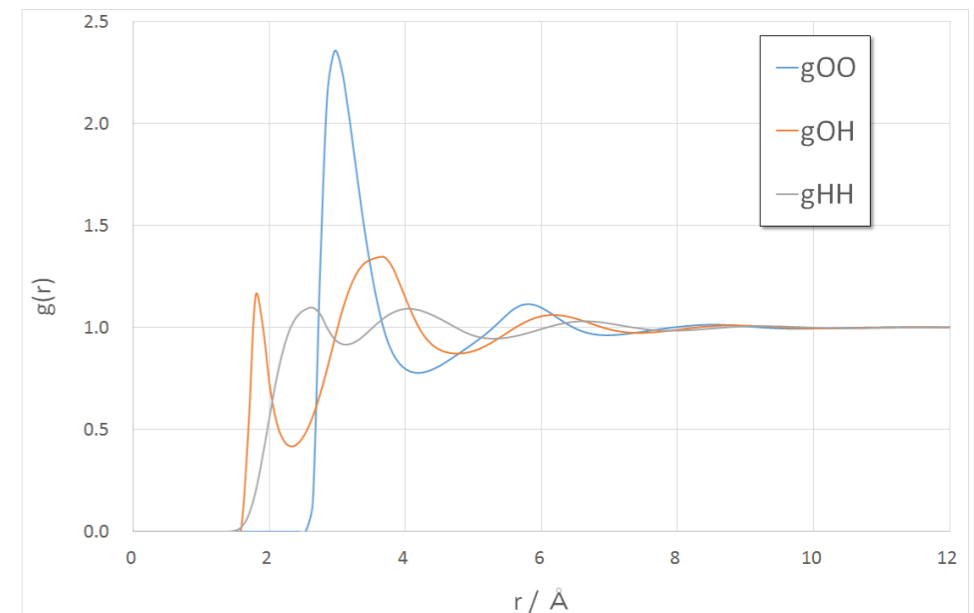
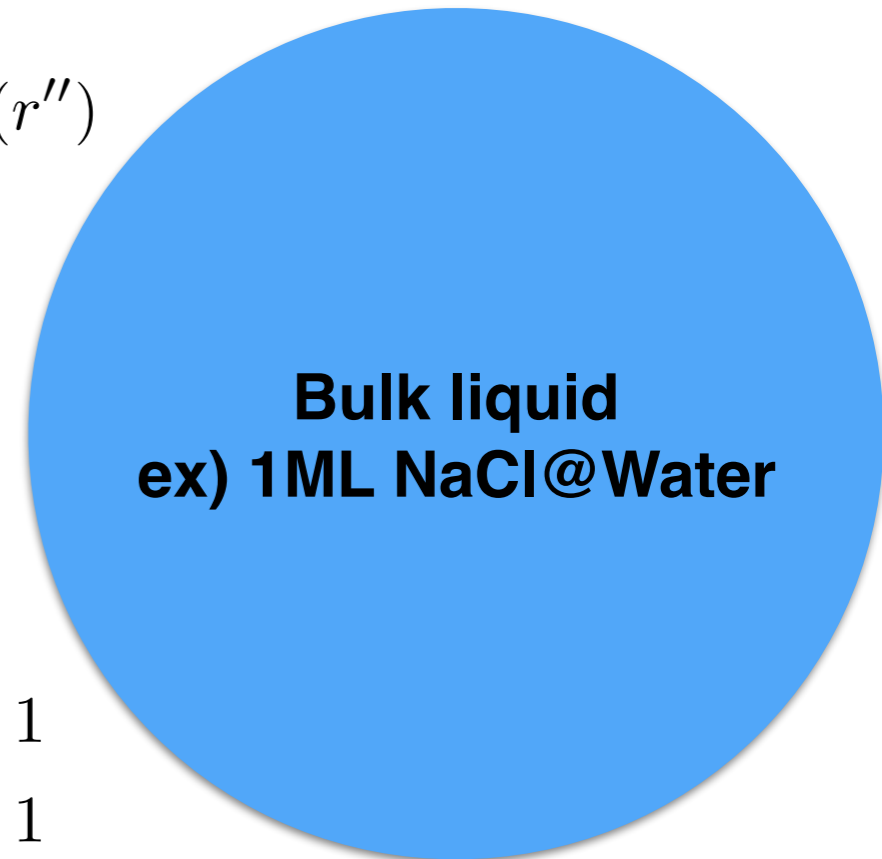
$$\begin{cases} h_{\alpha\gamma}(r) = \sum_{\mu\nu} \int d\mathbf{r}' \int d\mathbf{r}'' \omega_{\alpha\mu}(|\mathbf{r} - \mathbf{r}'|) c_{\mu\nu}(|\mathbf{r}' - \mathbf{r}''|) \chi_{\nu\gamma}(r'') \\ \omega_{\alpha\mu}(r) = \frac{1}{4\pi r^2} \delta(r - l_{\alpha\mu}) \\ \chi_{\nu\gamma}(r) = \omega_{\nu\gamma}(r) + \rho_{\gamma} h_{\nu\gamma}(r) \end{cases}$$

Closure relation (Kovalenco-Hirata)

$$g_{\alpha\gamma}(r) = \begin{cases} \exp[-\beta u_{\alpha\gamma}(r) + h_{\alpha\gamma}(r) - c_{\alpha\gamma}(r)] & \text{for } g_{\alpha\gamma} \leq 1 \\ 1 - \beta u_{\alpha\gamma}(r) + h_{\alpha\gamma}(r) - c_{\alpha\gamma}(r) & \text{for } g_{\alpha\gamma} > 1 \end{cases}$$

Interaction between atomic sites (Lennard-Jones + Coulomb)

$$\begin{cases} u_{\alpha\gamma}(r) = 4\epsilon_{\alpha\beta} \left[\left(\frac{\sigma_{\alpha\beta}}{r} \right)^{12} - \left(\frac{\sigma_{\alpha\beta}}{r} \right)^6 \right] + \frac{q_{\alpha} q_{\gamma}}{r} \\ \epsilon_{\alpha\beta} = \sqrt{\epsilon_{\alpha} \epsilon_{\gamma}} \\ \sigma_{\alpha\gamma} = \frac{\sigma_{\alpha} + \sigma_{\gamma}}{2} \end{cases}$$

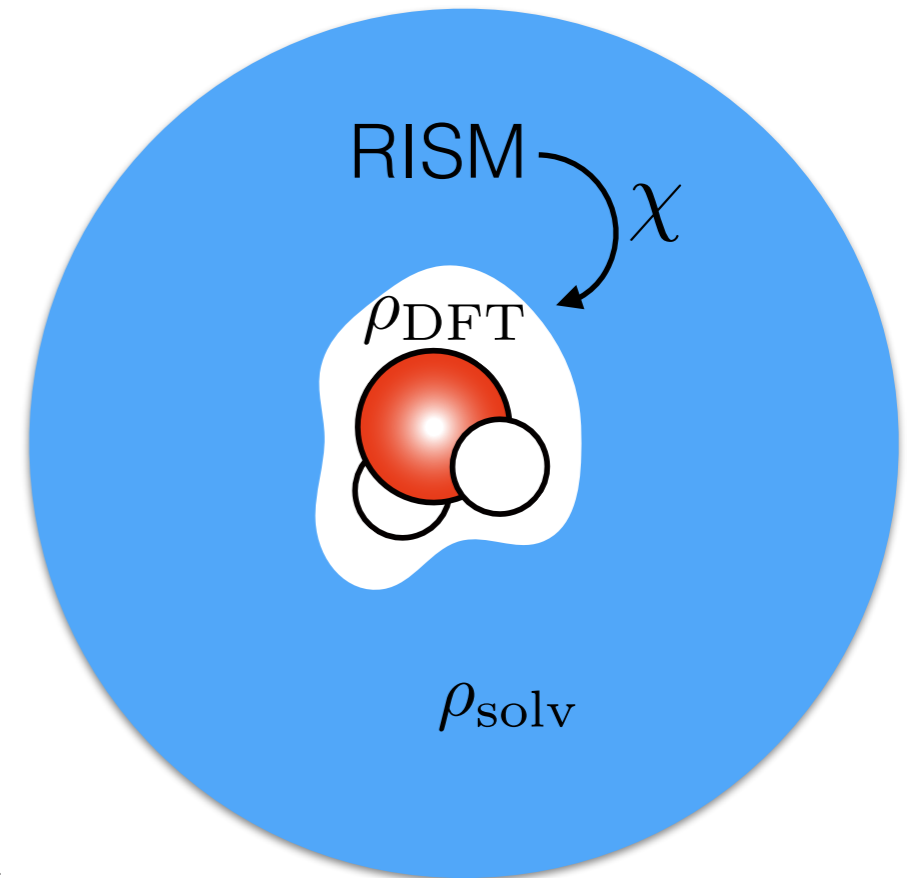


3D-RISM

3D-RISM equation

$$\begin{cases} \chi_{\nu\gamma}(\mathbf{r}) = \sum_{\mathbf{g}} \chi_{\nu\gamma}(\mathbf{g}) e^{i\mathbf{g}\cdot\mathbf{r}} \\ h_{\gamma}(\mathbf{r}) = \sum_{\nu} \int d\mathbf{r}' c_{\nu}(\mathbf{r}') \chi_{\nu\gamma}(\mathbf{r}' - \mathbf{r}) \end{cases}$$

From 1D-RISM

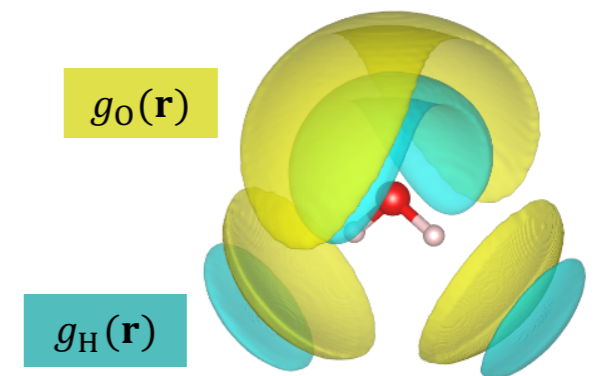


Closure relation (Kovalenco-Hirata)

$$g_{\gamma}(\mathbf{r}) = \begin{cases} \exp[-\beta u_{\gamma}(\mathbf{r}) + h_{\gamma}(\mathbf{r}) - c_{\gamma}(\mathbf{r})] & \text{for } g_{\gamma} \leq 1 \\ 1 - \beta u_{\gamma}(\mathbf{r}) + h_{\gamma}(\mathbf{r}) - c_{\gamma}(\mathbf{r}) & \text{for } g_{\gamma} > 1 \end{cases}$$

Interaction between atomic sites (Lennard-Jones + Coulomb)

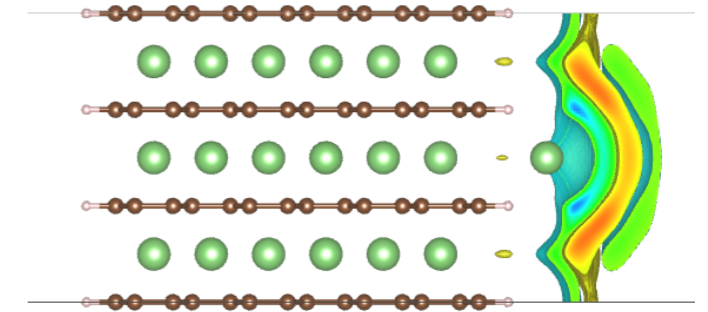
$$u_{\gamma}(\mathbf{r}) = \sum_A 4\epsilon_{\gamma A} \left[\left(\frac{\sigma_{\gamma A}}{|\mathbf{r} - \mathbf{R}_A|} \right)^{12} - \left(\frac{\sigma_{\gamma A}}{|\mathbf{r} - \mathbf{R}_A|} \right)^6 \right] + \int d\mathbf{r}' \frac{q_{\gamma} \rho_{DFT}}{|\mathbf{r} - \mathbf{r}'|}$$



Laue-RISM

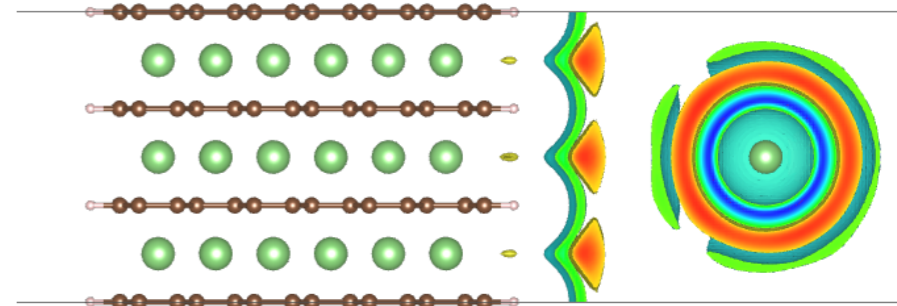
Laue-RISM equation From 1D-RISM

$$\begin{cases} \chi_{\nu\gamma}(\mathbf{g}_{\parallel}, z' - z) = \frac{1}{2\pi} \int_{-\infty}^{\infty} dg_z \chi_{\nu\gamma}(g) e^{ig_z(z' - z)} \\ h_{\gamma}(\mathbf{g}_{\parallel}, z) = \sum_{\nu} \int dz' c_{\nu}(\mathbf{g}_{\parallel}, z') \chi_{\nu\gamma}(\mathbf{g}_{\parallel}, z' - z) \end{cases}$$



Closure relation (Kovalenco-Hirata)

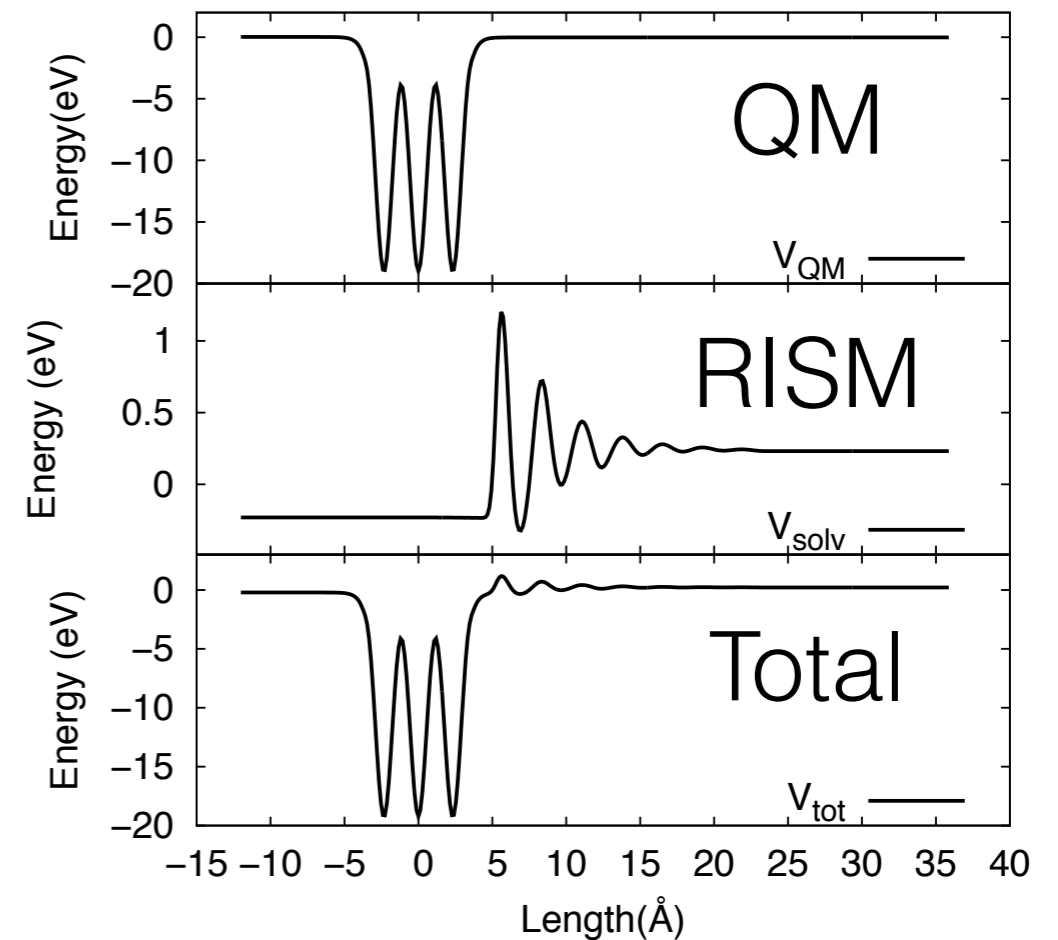
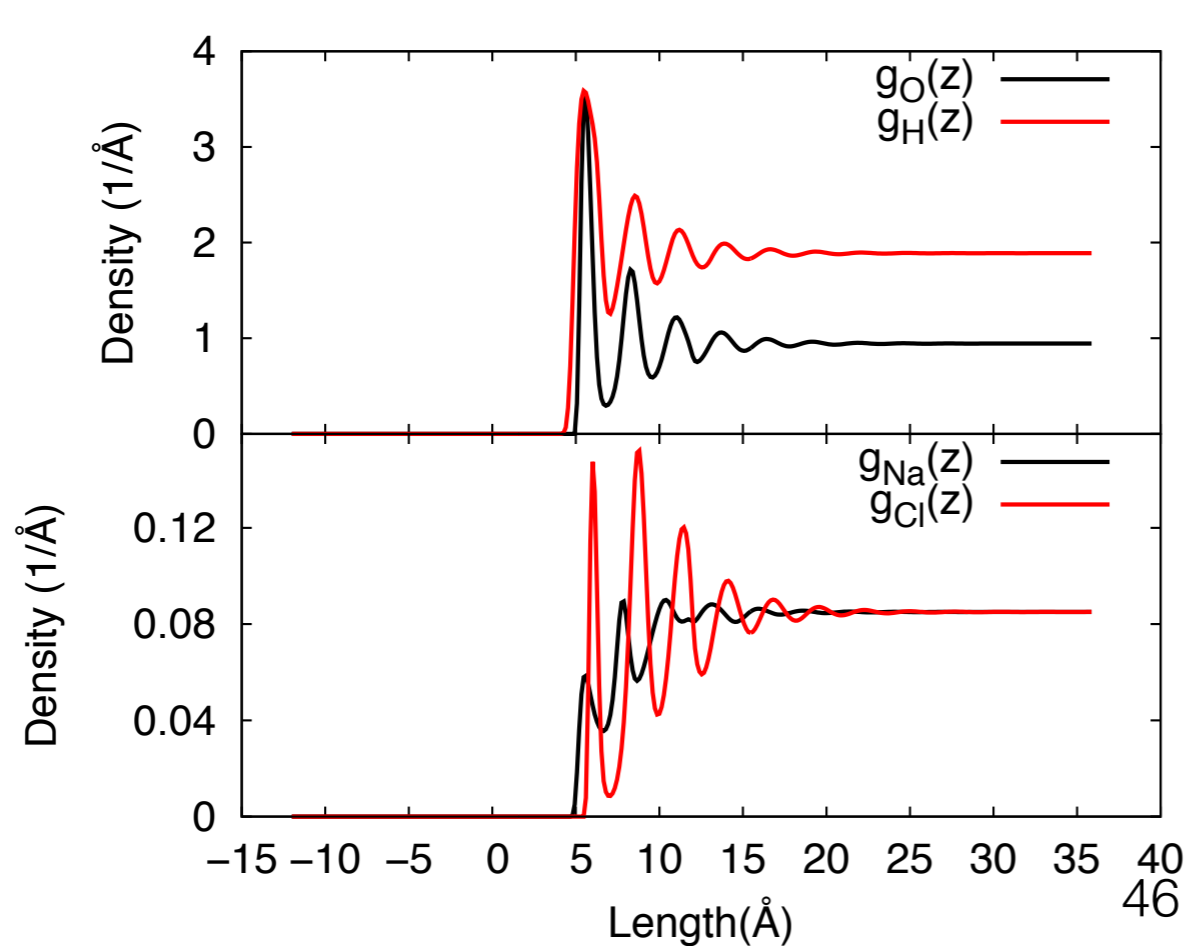
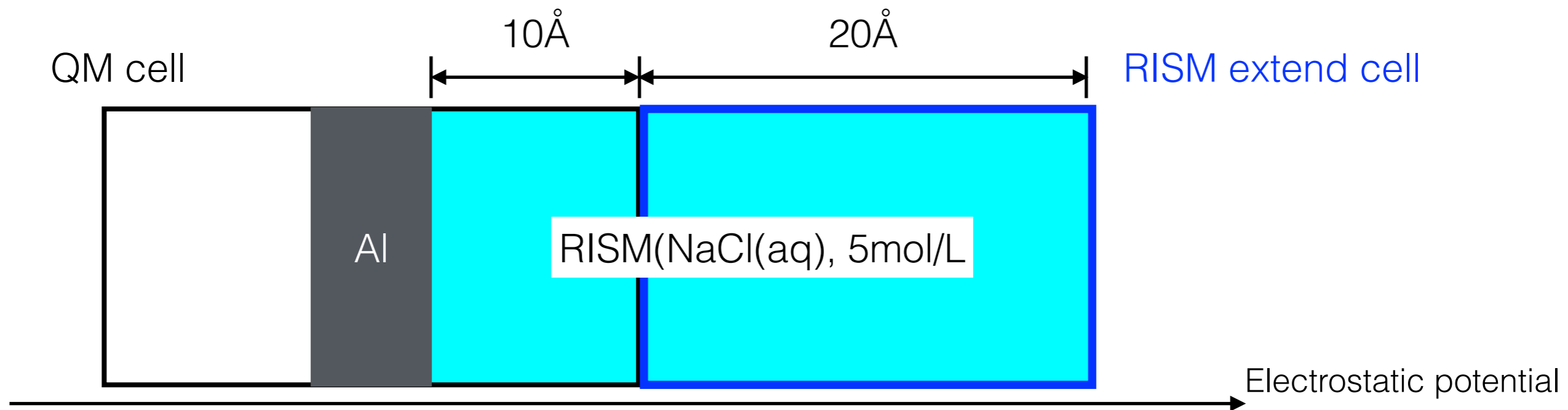
$$g_{\gamma}(\mathbf{r}) = \begin{cases} \exp[-\beta u_{\gamma}(\mathbf{r}) + h_{\gamma}(\mathbf{r}) - c_{\gamma}(\mathbf{r})] & \text{for } g_{\gamma} \leq 1 \\ 1 - \beta u_{\gamma}(\mathbf{r}) + h_{\gamma}(\mathbf{r}) - c_{\gamma}(\mathbf{r}) & \text{for } g_{\gamma} > 1 \end{cases}$$



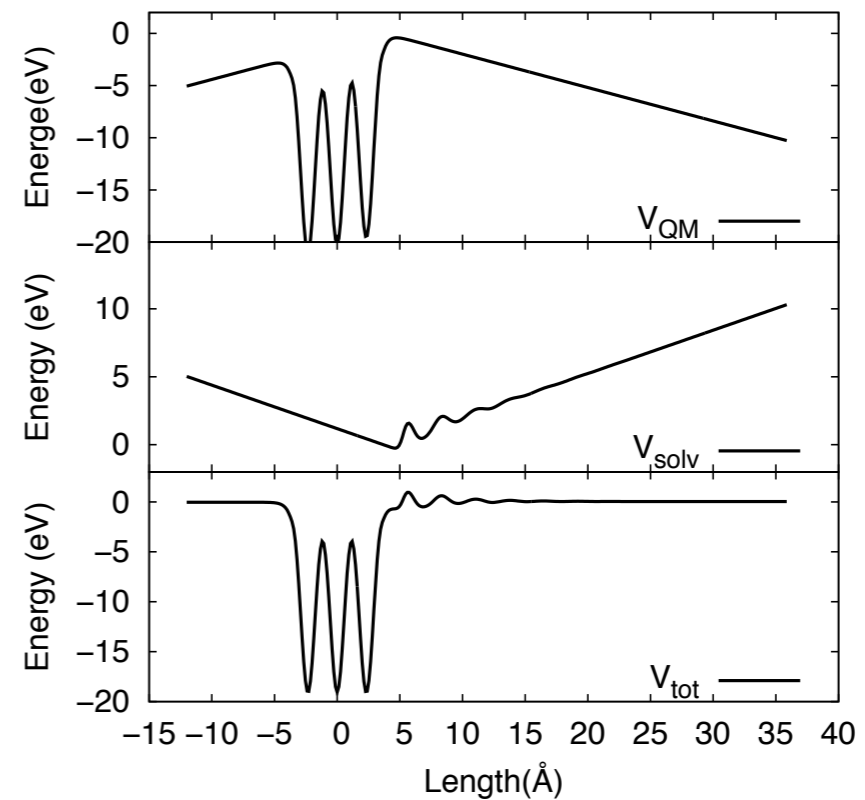
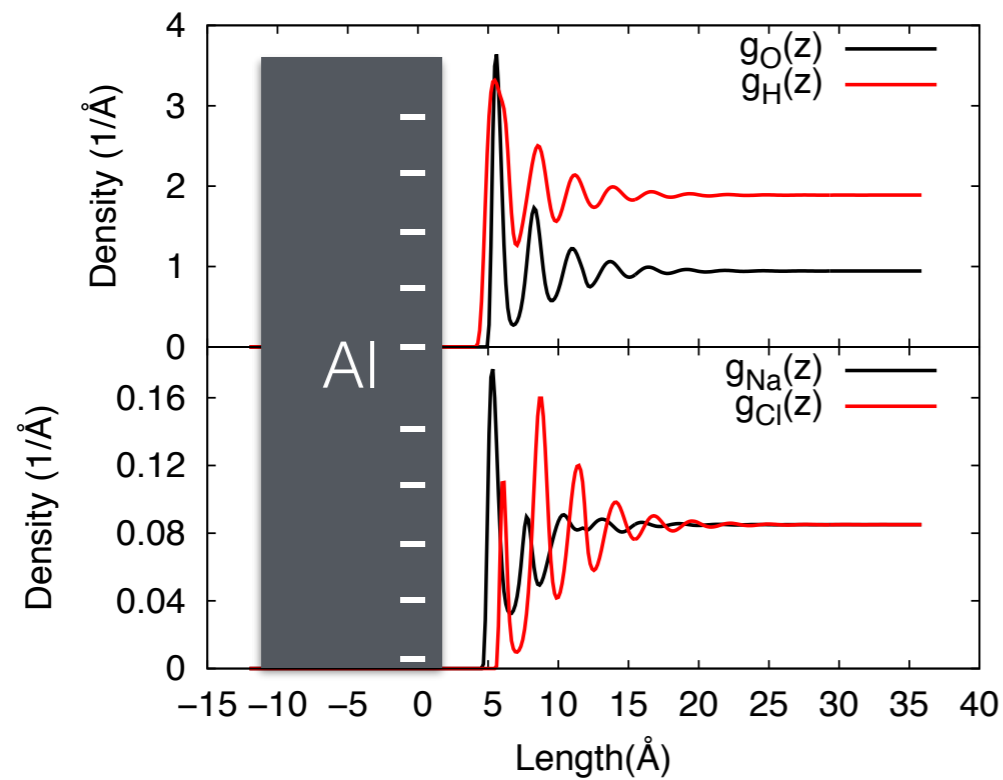
Interaction between atomic sites
(Lennard-Jones + Coulomb)

$$u_{\gamma}(\mathbf{r}) = \sum_A 4\epsilon_{\gamma A} \left[\left(\frac{\sigma_{\gamma A}}{|\mathbf{r} - \mathbf{R}_A|} \right)^{12} - \left(\frac{\sigma_{\gamma A}}{|\mathbf{r} - \mathbf{R}_A|} \right)^6 \right] + \int d\mathbf{r}' G^{\text{MBC}}(\mathbf{r}, \mathbf{r}') \rho_{\text{DFT}}(\mathbf{r}')$$

Al - NaCl aqueous interface



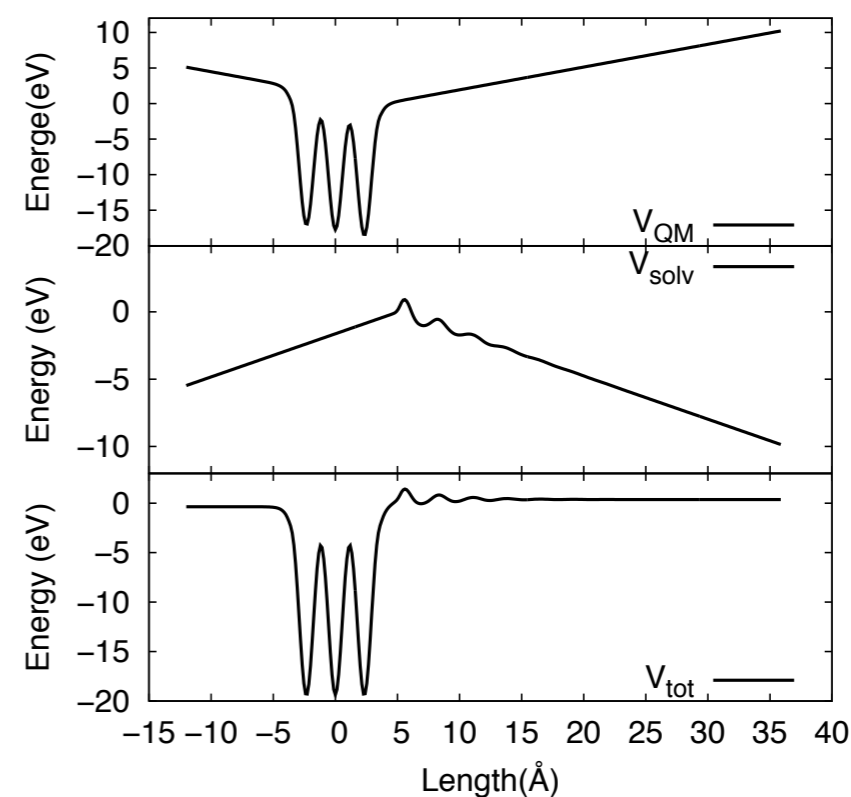
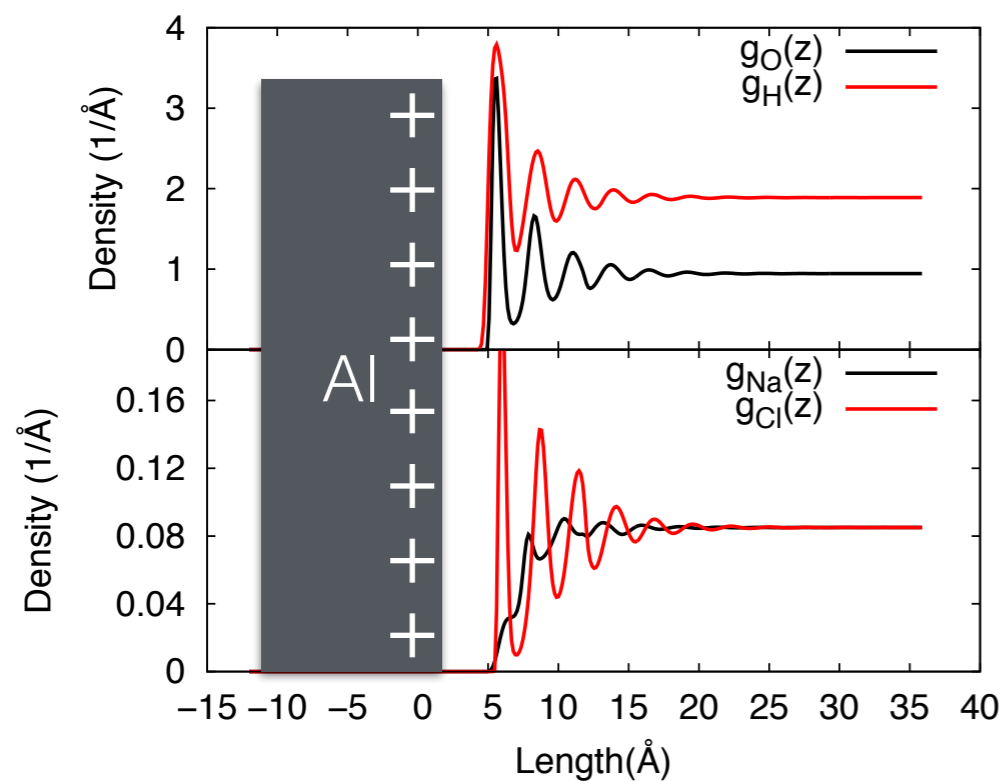
Al/NaCl溶液界面(電気二重層)



QM

RISM

Total

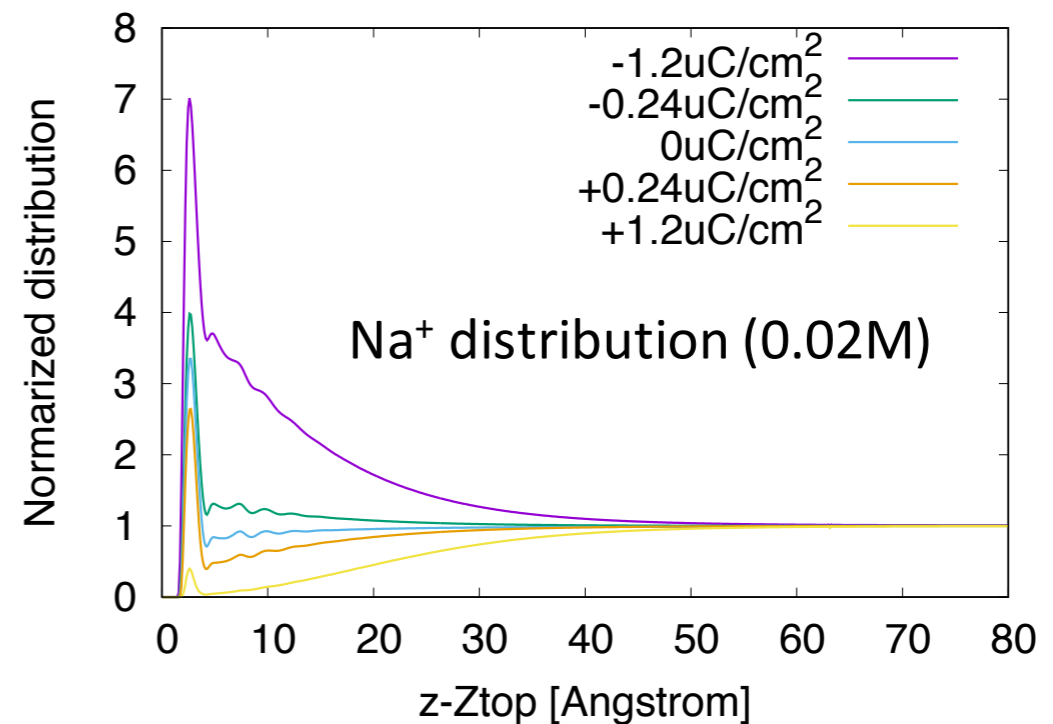
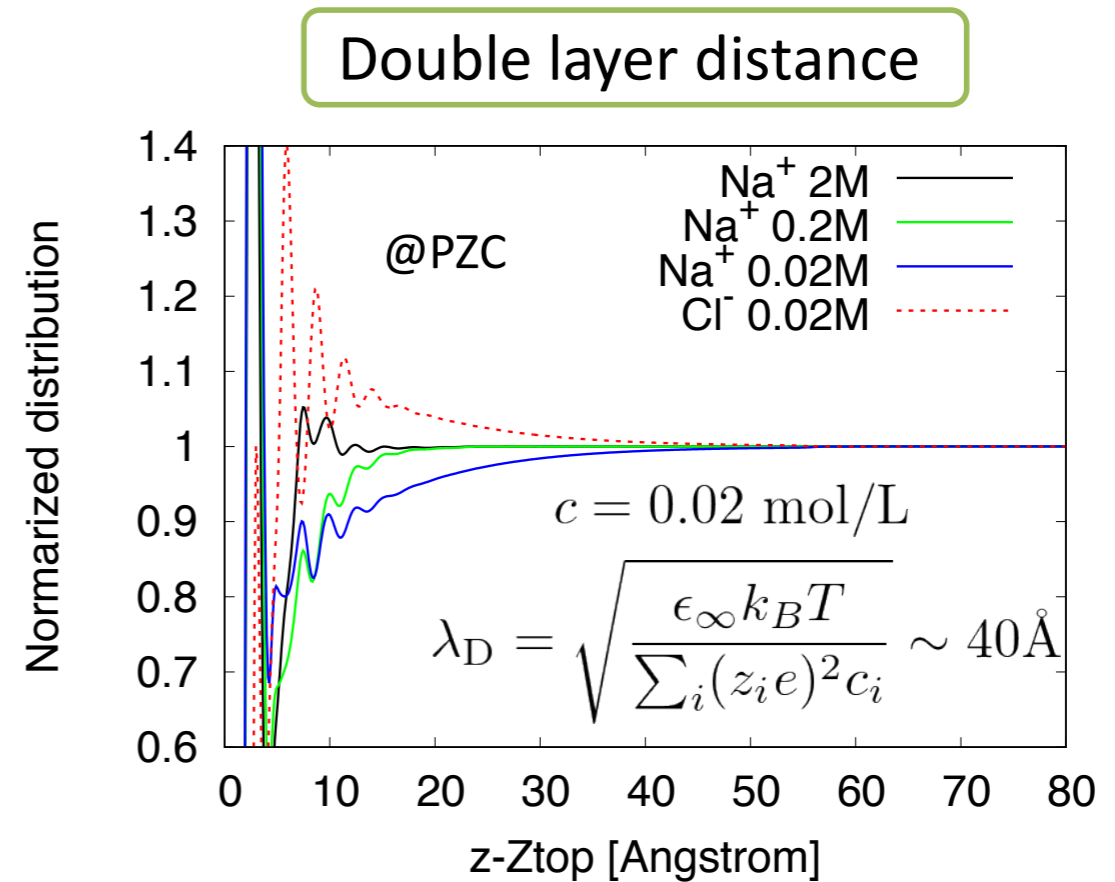
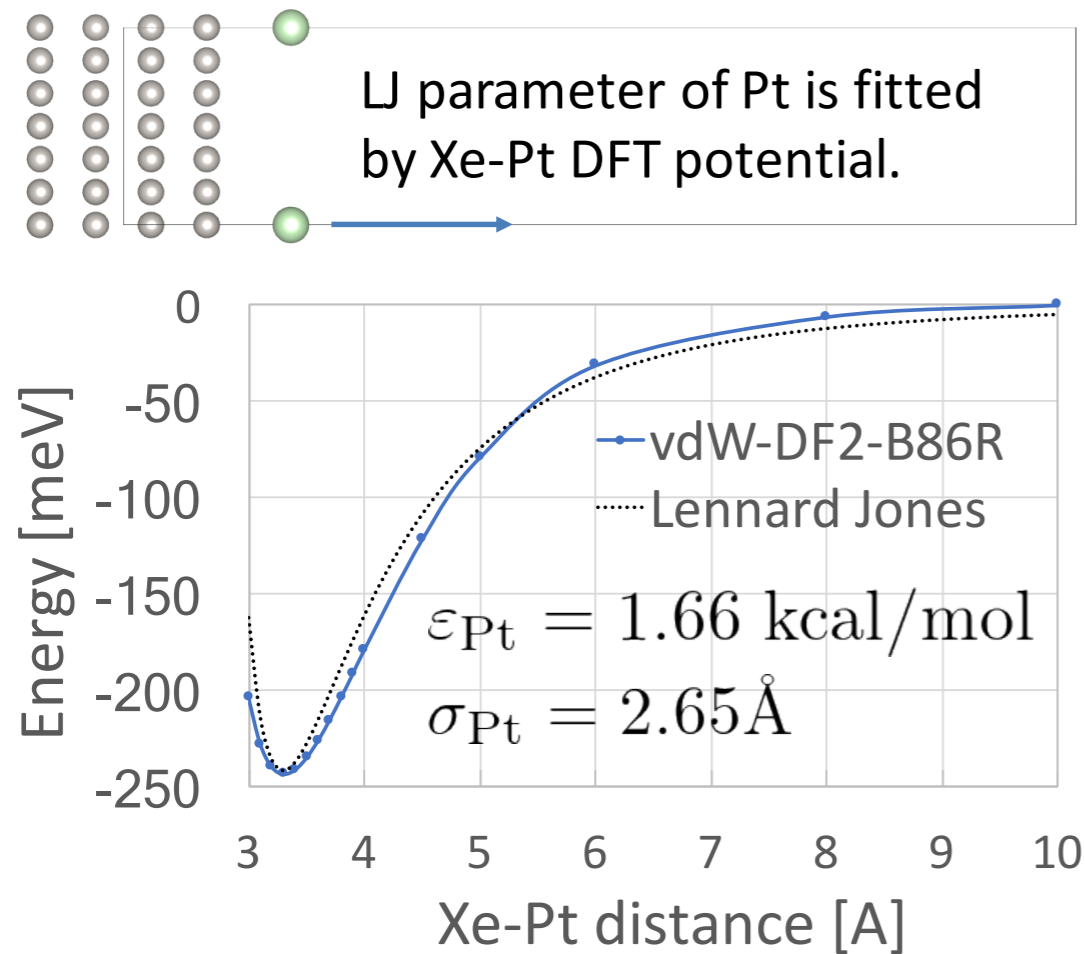


QM

RISM

Total

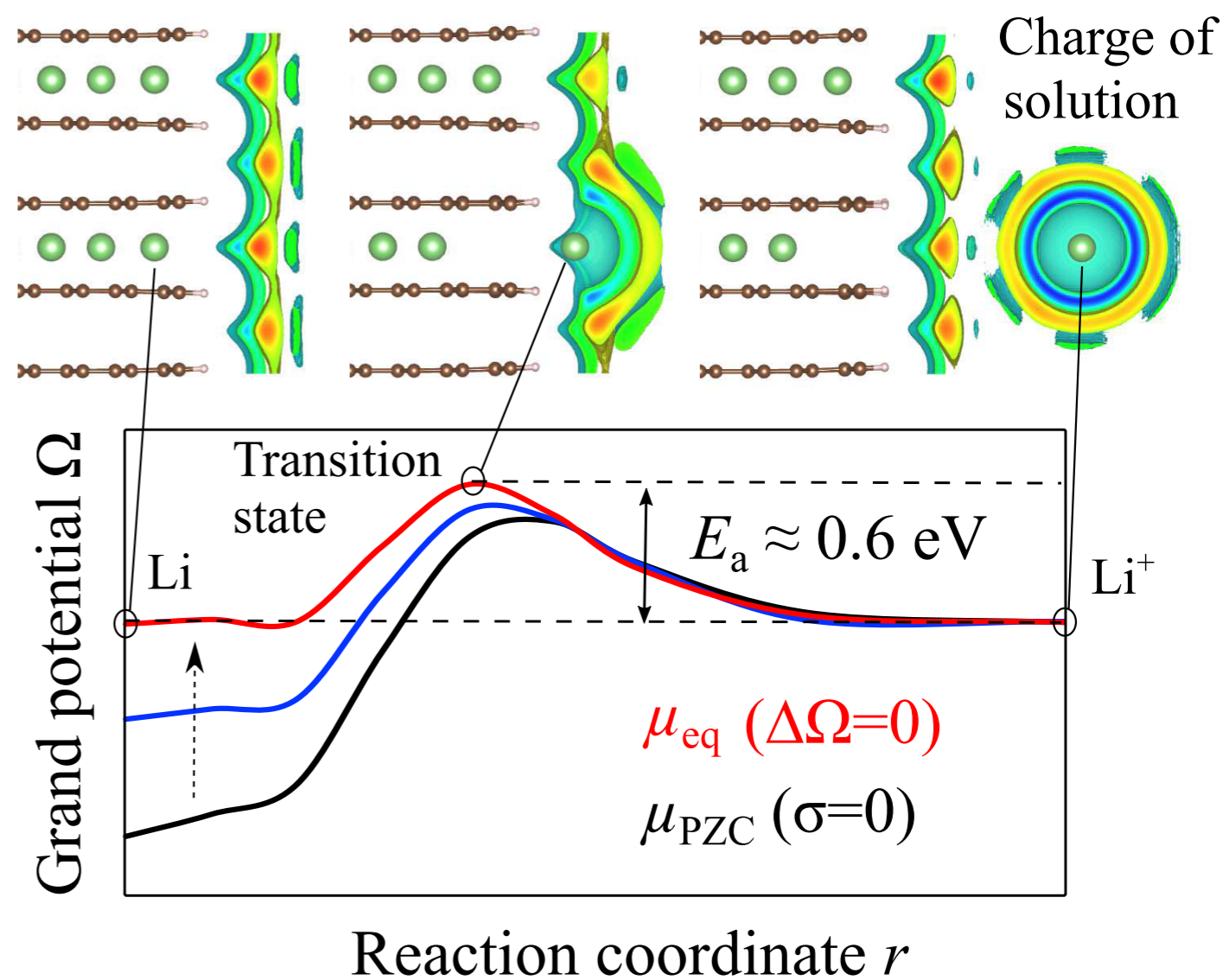
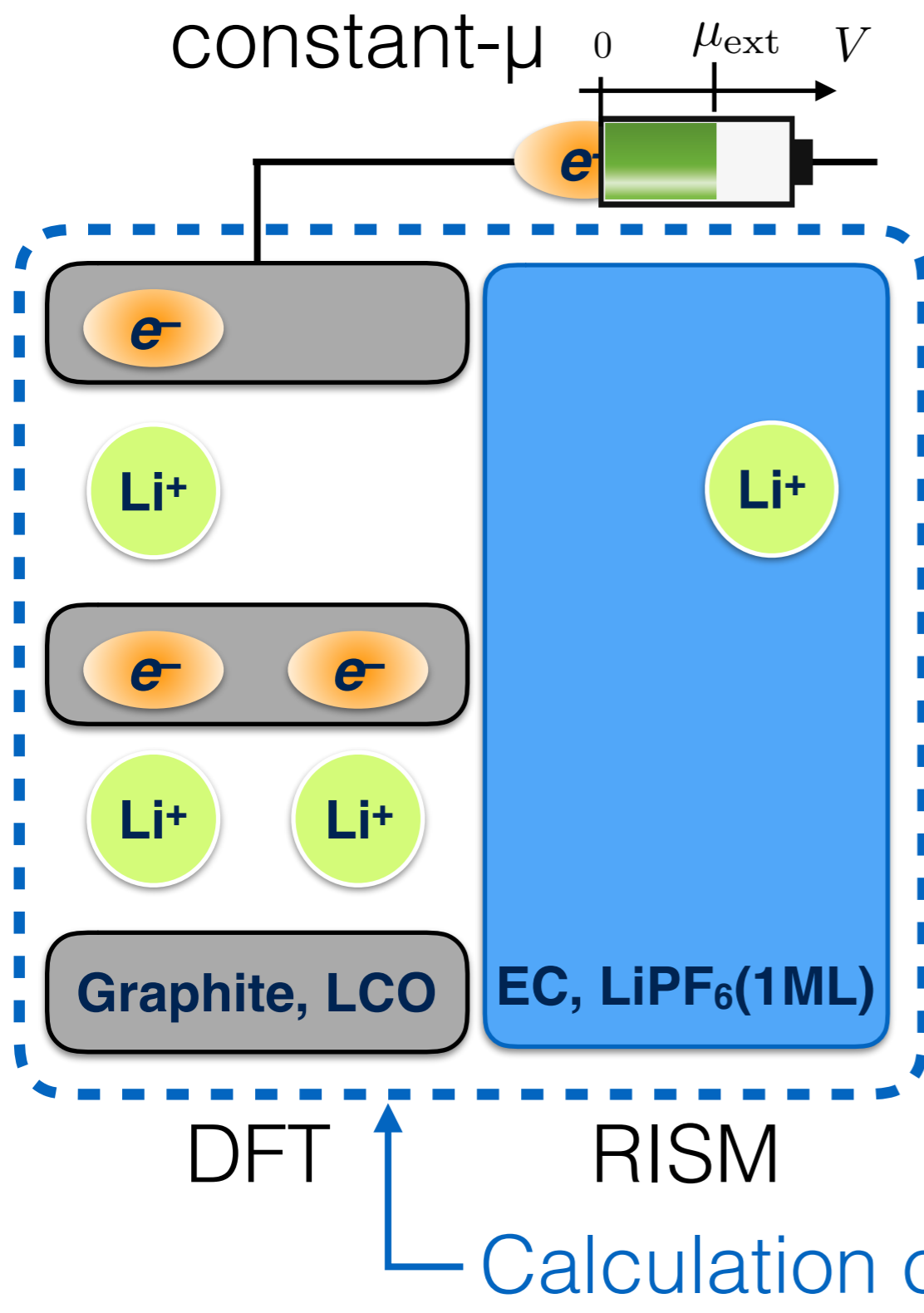
RISM vs. Debye Hückel



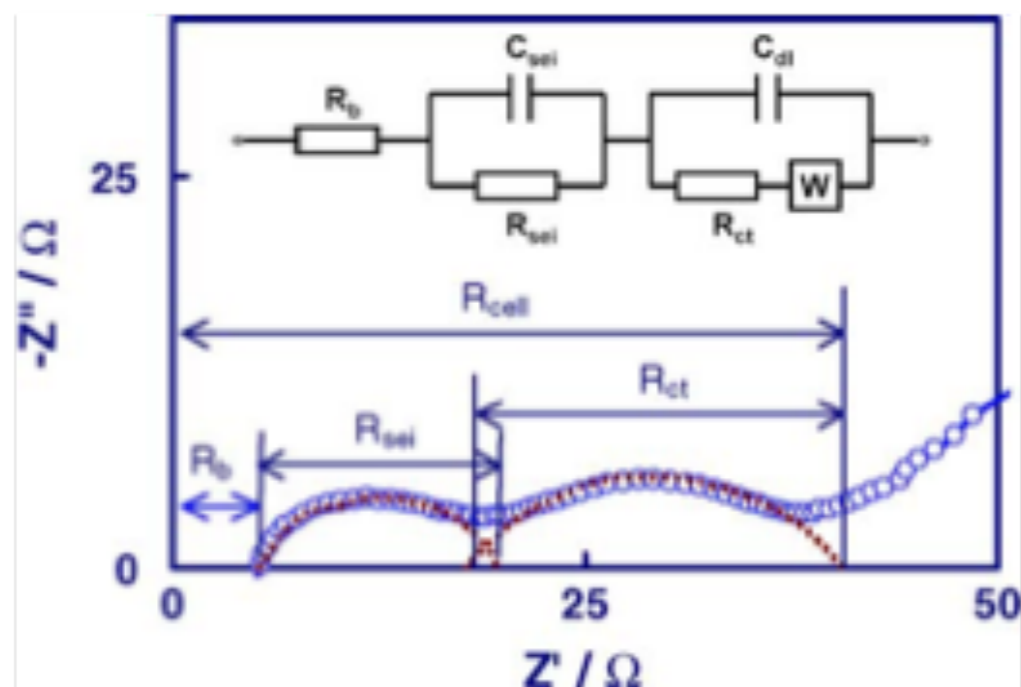
Outline

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Solvation process of Li-ion



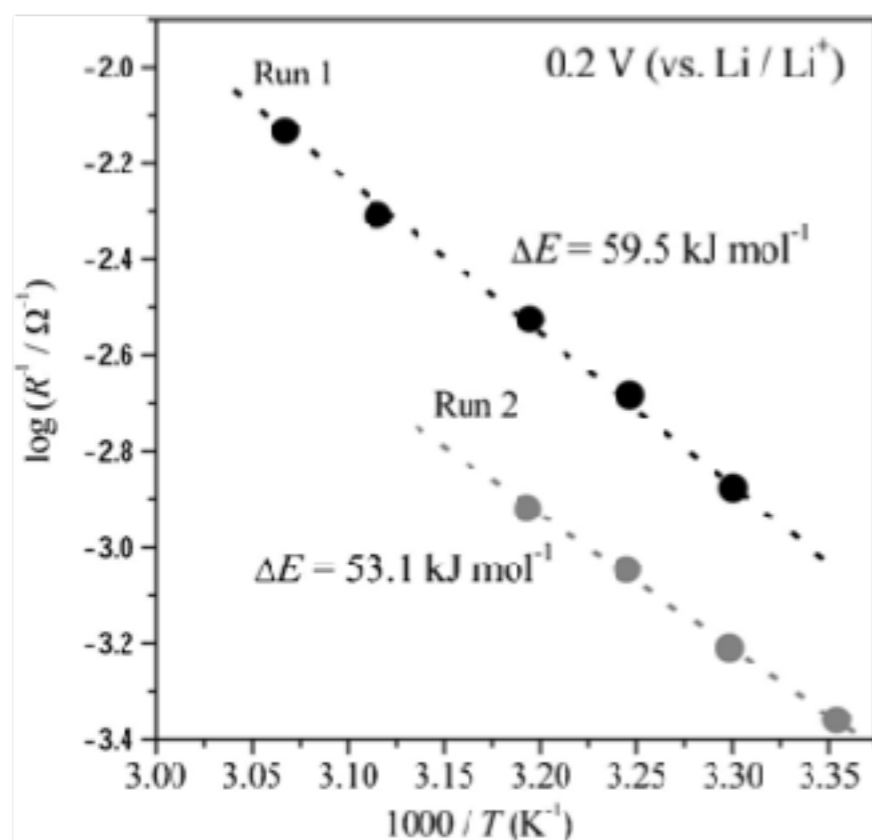
Electrochemical impedance spectroscopy (EIS) measurements



Typical EIS of Conventional LIB cell
LiCoO₂ | EC3:EMC7 LiPF₆ 1M | Graphite

In the fully charged and discharged states as well as at the low temperatures ($\leq 20^\circ\text{C}$), the R_{cell} of the Li-ion cells is **predominated** by the R_{ct} .

S. S. Zhang, K. Xu, and T. R. Jow, *Electrochimica Acta* **49**, 1057 (2004).

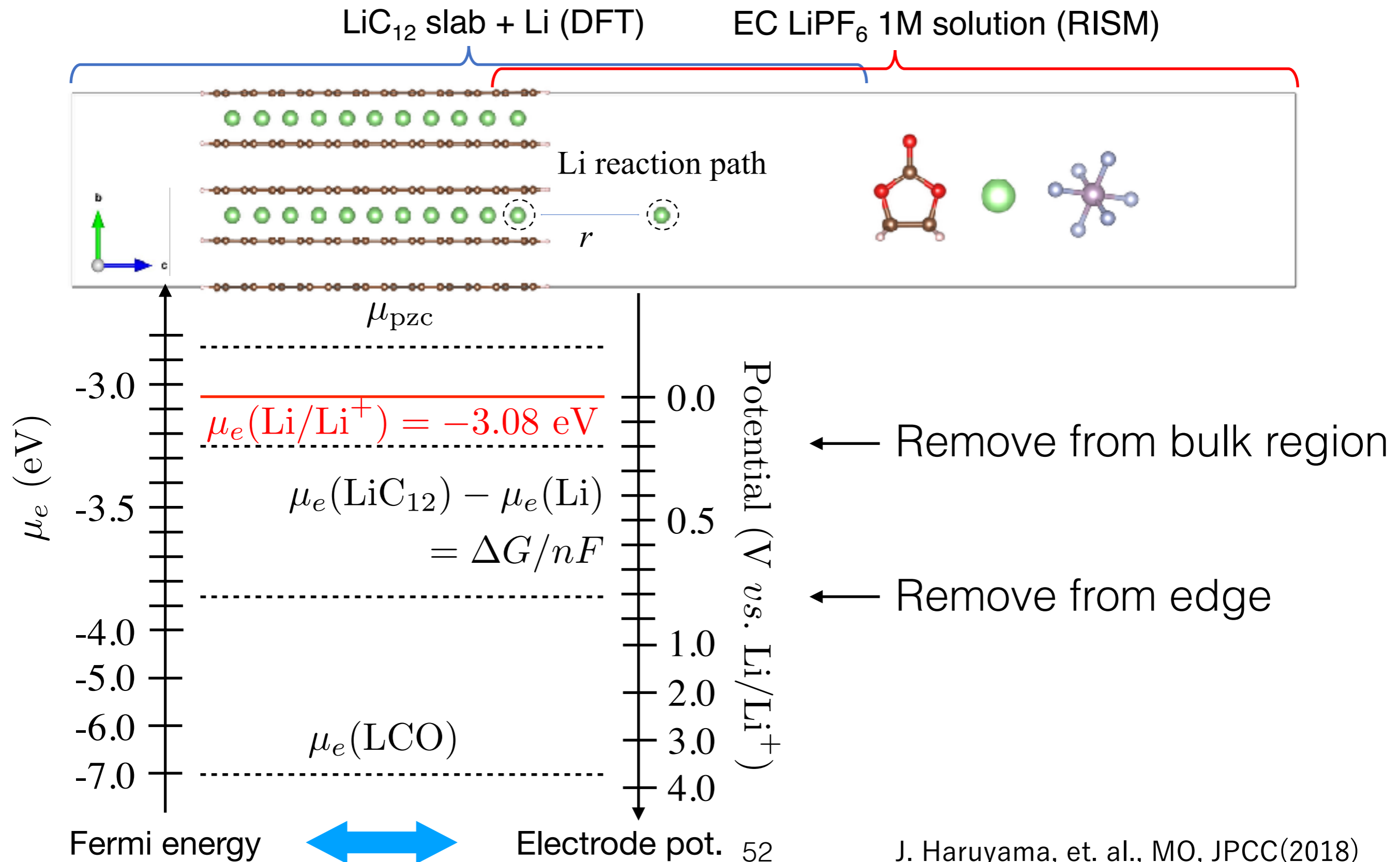


Temperature-dependence of R_{ct} @ $0.2 \text{ V vs. Li/Li}^+$

The activation energies were evaluated to be around 50-60 kJ/mol (**0.5-0.6 eV**). These values are very large compared to lithium ion conduction in active materials.

T. Abe, H. Fukuda, Y. Iriyama, and Z. Ogumi, *J. Electrochem. Soc.* **151**, A1120 (2004).

Definition of the electrode potential (Calculation)



Summary

- We have developed a series of simulation methods to simulate the electrode/electrolyte interface.
- We can define the reference electrode potential which is consistent with thermodynamics and electrochemistry.
- Our simulation technique is applicable many electrochemical systems, such as secondary ion batteries, fuel cells, collision, electroplating, ion exchange membrane